

SCREEN IR Day 2025

Investor Relations
Corporate Communications Department
SCREEN Holdings Co., Ltd.



Cautionary statements:

- The earnings forecasts, contained in these materials and communicated verbally, are made in accordance with currently available information and rational assumptions. SCREEN Holdings does not promise that the forecasts or estimates will be accurate. Therefore, it should be noted that actual results could differ significantly due to a variety of factors.
- Figures are rounded down to eliminate amounts less than ¥100 million, except per share figures. Ratios are rounded off.
- SCREEN's fiscal year (FY) covers the period from April 1 to March 31 of the following calendar year. (e.g. FY2026/03 = April 1, 2025 - March 31, 2026)

Agenda

■ SCREEN Group’s growth strategy 20 min

■ Q&A session 25 min

----- Intermission (10 min) -----

■ SPE wet etching and cleaning trends 20 min

■ Advanced packaging trends and outlook 15 min

■ Q&A session 25 min

For in-person participants only:

■ IIC Tokyo tour 30 min

■ Social gathering 60 min

Introduction of our CEO

Masato Goto

Representative Director, President and CEO
SCREEN Holdings Co., Ltd.

Place of birth: Tokyo

Hobbies: Camping, kayaking, smoke cooking



- 1990** Joined Dainippon Screen Mfg. Co., Ltd. (now SCREEN Holdings)
- 1995** Seconded to DAINIPPON SCREEN ENGINEERING OF AMERICA, LLC.
- 2001** Seconded to DAINIPPON SCREEN (DEUTSCHLAND) GmbH
- 2009** Head of Production, Semiconductor Equipment Company
- 2011** Vice President, Semiconductor Equipment Company
- 2014** Director, SCREEN Semiconductor Solutions Co., Ltd.
- 2019** Representative Director and President, SCREEN Semiconductor Solutions Co., Ltd.
- 2024** Senior Managing Executive Officer, Head of Corporate Strategy, SCREEN Holdings Co., Ltd.
- 2025** Representative Director, President and CEO, SCREEN Holdings Co., Ltd.

SCREEN Group's growth strategy

SCREEN Holdings Co., Ltd.

Masato Goto
Representative Director,
President & CEO



Paving the way for SCREEN's future growth

Corporate Philosophy

Purpose

Innovation for a Sustainable World

Sharing the Future	Building a better future for society with commitment and integrity
Personal Development	Realizing everyone's full potential through trust and teamwork
The Pursuit of Technological Excellence	Exploring technologies while integrating with innovative collaboration

Founder's Motto

Shi Ko Ten Kai Broadening everyone's thoughts and horizons for innovation

Building a world that truly values humans

Nothing can replace real communication that connects people. That is why human-technology synergy is increasingly important.

The SCREEN Group is engaged in multiple, diverse businesses, including our mainstay SPE business and original printing-related business, but a common thread connecting all of them is the capability to contribute to the development of communication tools through technology.

This, I firmly believe, is where our corporate purpose lies. By providing solutions from multiple angles through our business activities, and connecting humans and technology, we aim to become indispensable to society.

SCREEN at a glance

Year founded

1868

Year established

1943

Net sales

¥625.2 bn

Operating margin

21.7%
FY2025/03

Market capitalization
as of November 30, 2025

¥1,226.1 bn

Group employees

6,415

Credit rating*

A+

Outlook: Stable

* Long-term issuer rating by the Japan Credit Rating Agency, Ltd. (JCR)

2024 market share*

SPE

No. 1 global share

Single wafer cleaning equipment

No. 1 global share

Batch-type cleaning equipment

No. 1 global share

Spin scrubbers

GA

No. 1 global share

POD equipment (roll-fed inkjet printing)

Top-class global share

CTP equipment

FT

No. 1 global share

Coater/developers

PE

Top-class global share

Direct imaging systems for solder resists

* Market shares are based on equipment category totals, including data from SCREEN, in a calendar year basis.

Agenda

■ 10-year vision and roadmap

■ Value Up Further 2026

– Cash allocation

- a. Growth investment
- b. Our new R&D center

– Shareholder returns

– Business growth strategy

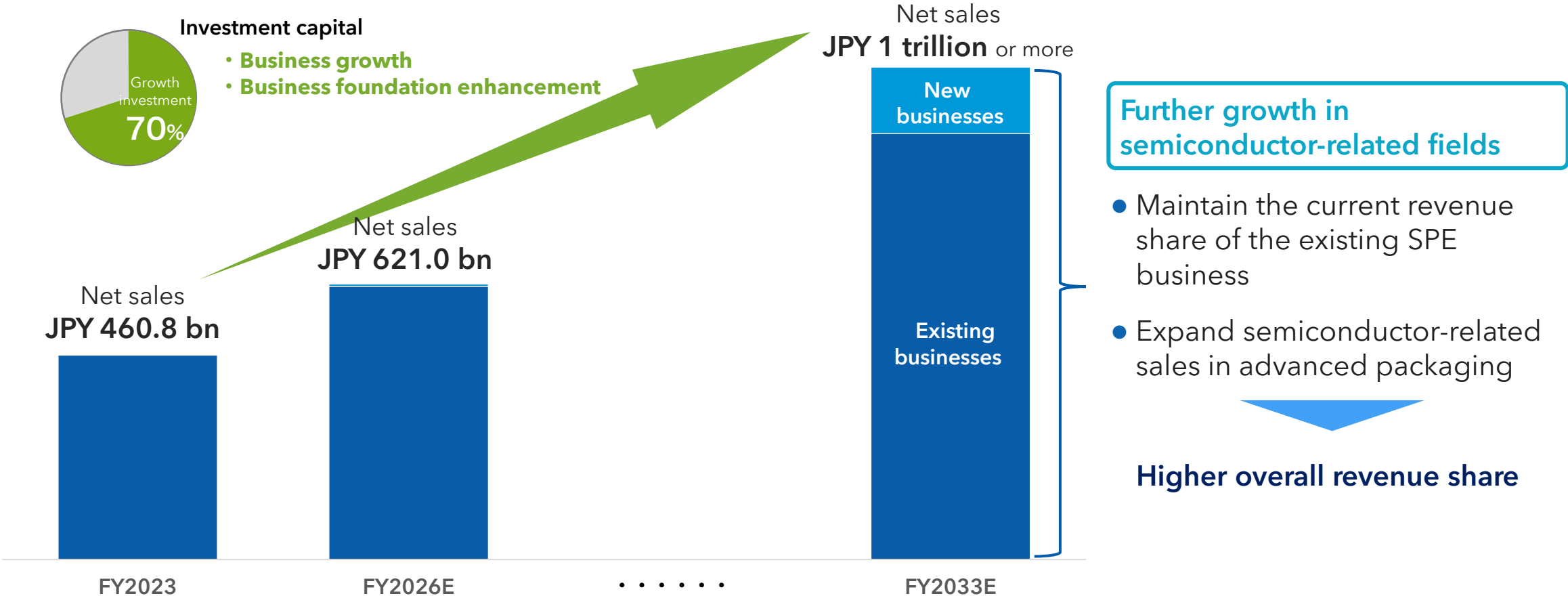
- a. Portfolio management
- b. Core technologies redefined
- c. Progress toward the 3-yr financial targets
- d. New business and innovation management

■ Summary

Financial & non-financial targets in the Management Grand Design

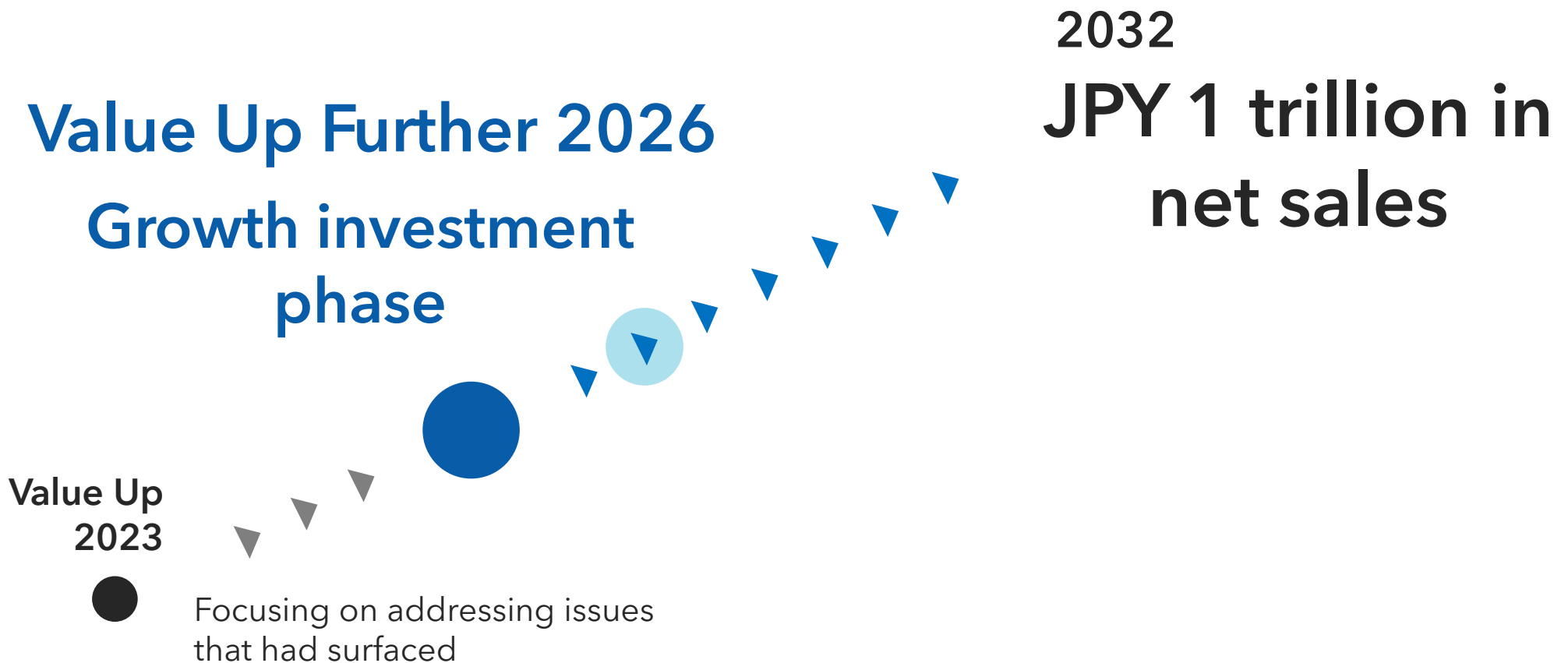
10-year vision for enhancing corporate value

Basic policy: To grow our existing businesses and create new businesses, 70% of our investment fund* will be allocated to growth, with the aim of achieving the Management Grand Design’s FY2033/03 targets of net sales of ¥1 trillion or more and an operating margin of 20% or above.



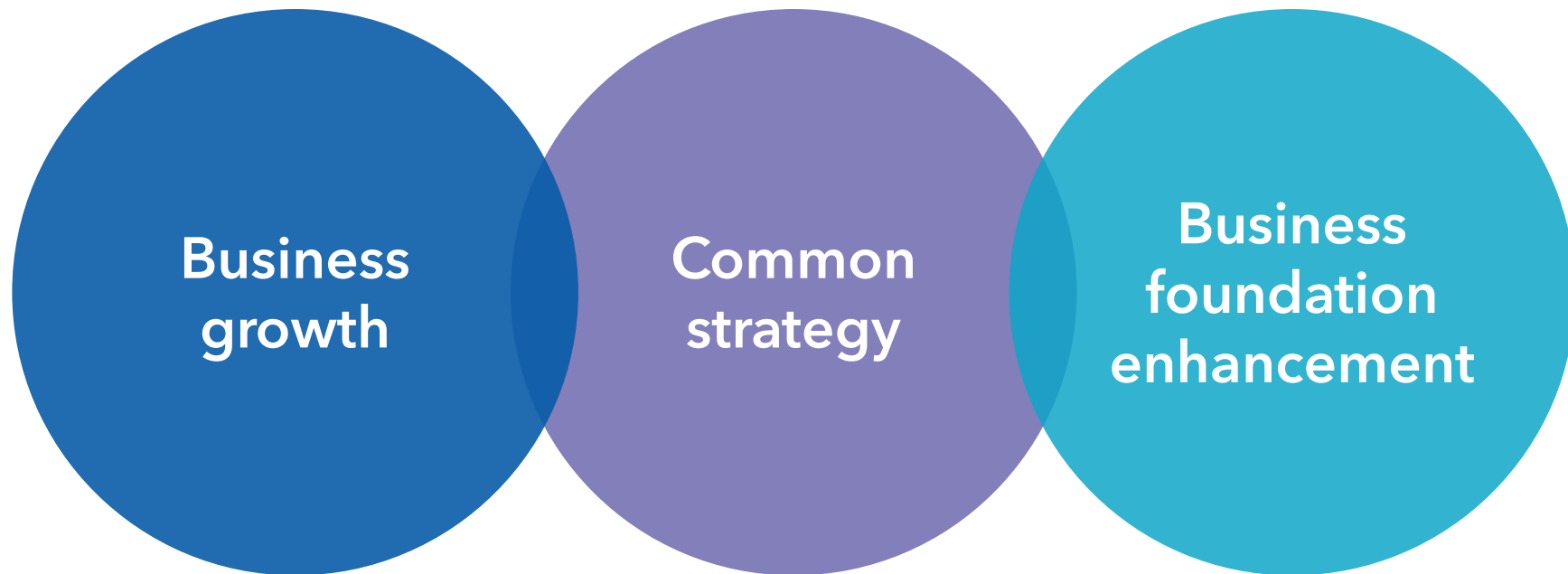
*Operating cash flow before research expenses

Moving to the growth investment phase: a step beyond existing business growth

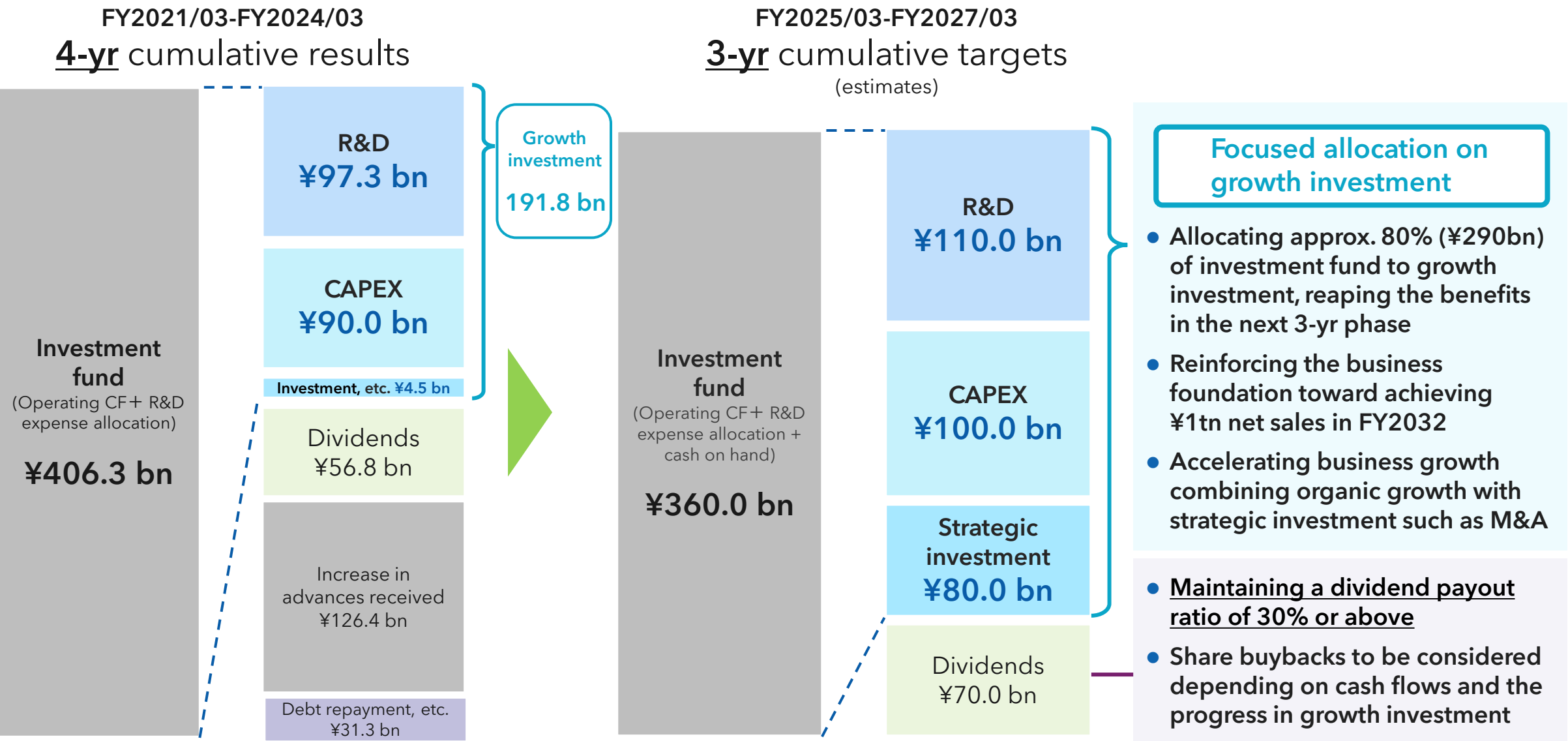


Paving a solid path for growth

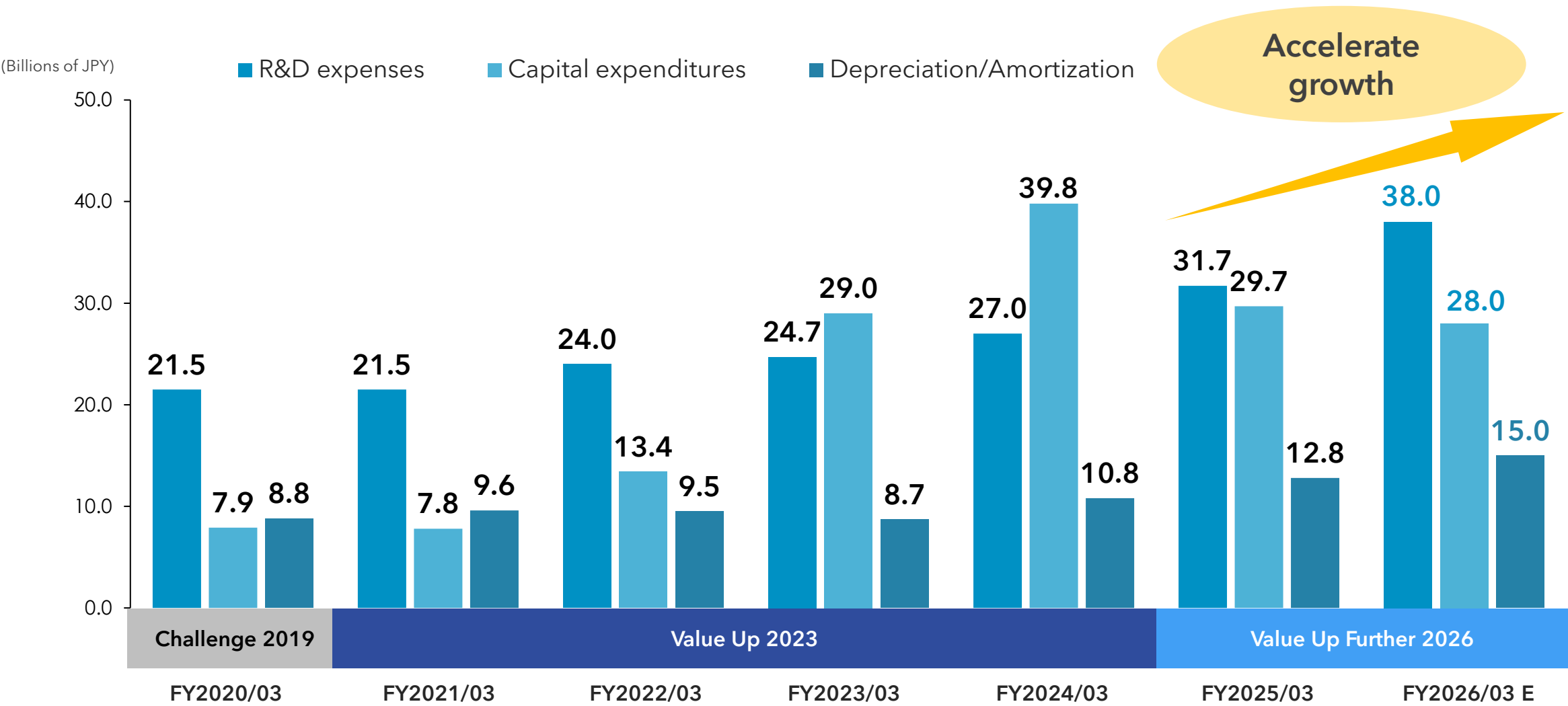
While maintaining the high profitability and efficiency achieved under Value Up 2023, we are dedicating the current three-year phase to **building a foundation for sustainable growth**.



Value Up Further 2026: Cash allocation (3-yr cumulative)



Value Up Further 2026: Growth investment



Value Up Further 2026: Strategic investment

1

Accelerate the growth of advanced packaging business

- ▶ Development of Cu-Cu low-temperature hybrid bonding
Acquisition of an R&D business in wafer bonding from Nikon
- ▶ Expanding product portfolio for PLP coaters and direct imaging systems

2

Advance the development of world-leading wet clean technology Enhance product competitiveness in SPE

ATCA, an overseas R&D center for semiconductor manufacturing processes to be established in Albany, New York

- Acquired land in Yasu City, Shiga
- Acquired production site and building in Nagaokakyo City, Kyoto Prefecture
- Life Sciences: Acquired shares of Kyo Diagnostics and made it a subsidiary
- GA: Acquired Germany-based CGS as a group company

Our new R&D center

Overview of ATCA

● Objective

To i) accelerate elemental technology validation and equipment development for our global SPE business, and to ii) shorten the time required for elemental technology validation by conducting leading-edge device characterization on site.

● R&D facility

ATCA will be located within Albany NanoTech Complex, the state-of-the-art semiconductor facility operated by NY Creates (NYCR).

It will be using NYCR's clean room and other infrastructure to pursue solo research as well as joint research with global partners.

› We will aim to increase our presence in wet cleans as well as thermal processing and advanced packaging.



Our new R&D center

Overview of ATCA

● Company information

Company name	SCREEN Advanced Technology Center of America, LLC (ATCA)
Location	201 Fuller Road, Suite 306, Albany, NY 12203, U.S.A.
Representative	Ian Brown, PhD, President
Established	December 1, 2025

● Facility information

Floor area	Clean room: 929 m ² Office space: 462 m ²
Main purpose	R&D for leading semiconductor production processes and equipment
Total investment	Around JPY 12.0 billion expected by March 31, 2027, excluding other expenses

Role of the new R&D center

- Working with IBM to develop leading-edge device processes and conduct device characterization near our clients.
- Serving our clients worldwide by developing new machines featuring our most advanced technologies.

Rakusai
@Kyoto



Elemental technology development,
including seeds search

PTC
@Hikone



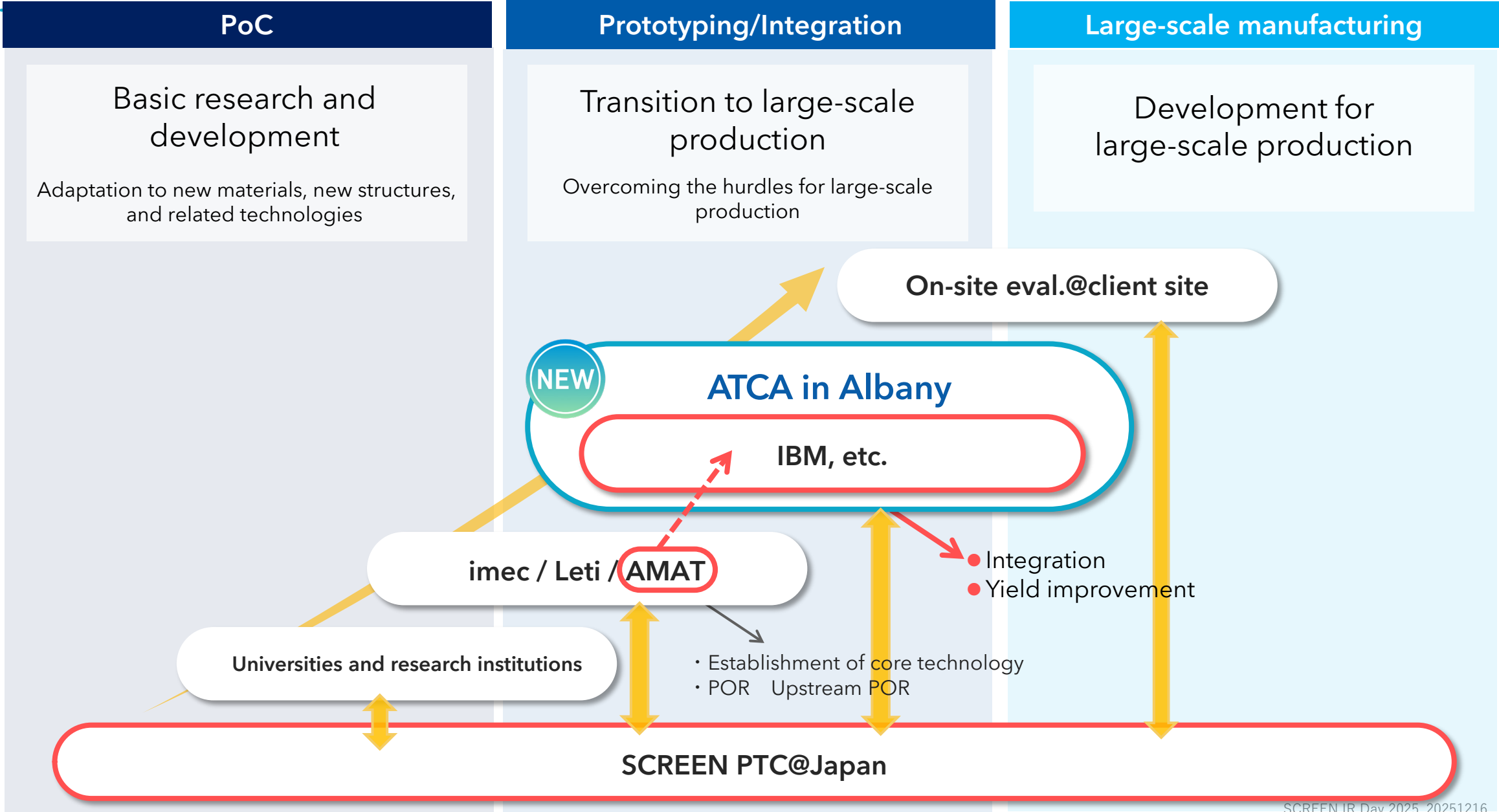
Mechanical development in collaboration with
manufacturing and engineering teams

ATCA
@Albany

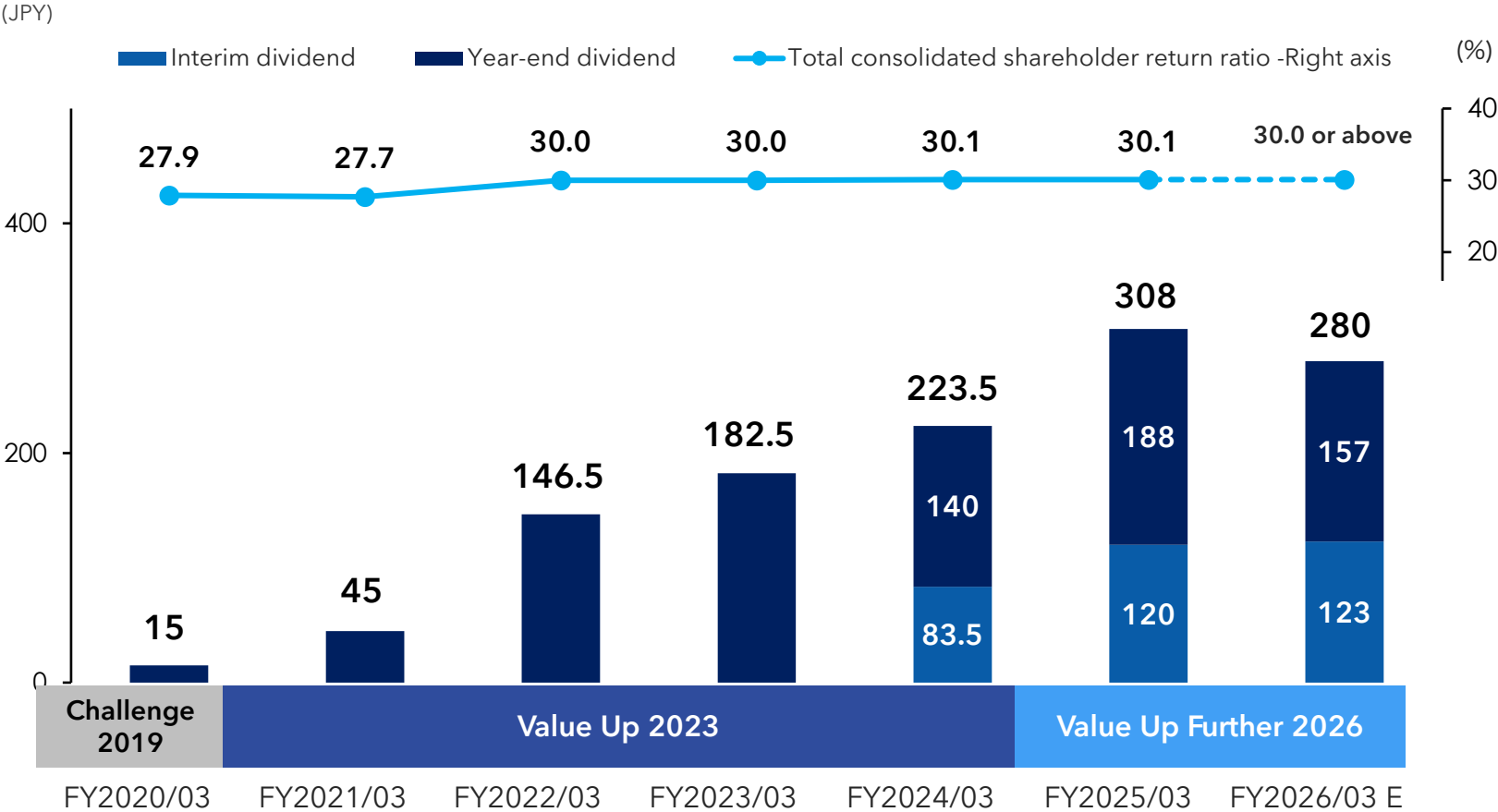


Solo research and joint research projects
in collaboration with global partners

Our R&D pipelines



Value Up Further 2026: Shareholder returns



Note: The Company implemented a stock split of common stock in the ratio of 1 share into 2 shares on October 1, 2023.
The dividend per share is calculated based on the assumption that the stock split was conducted at the beginning of the fiscal year ended March 2020.

Shareholder return policy

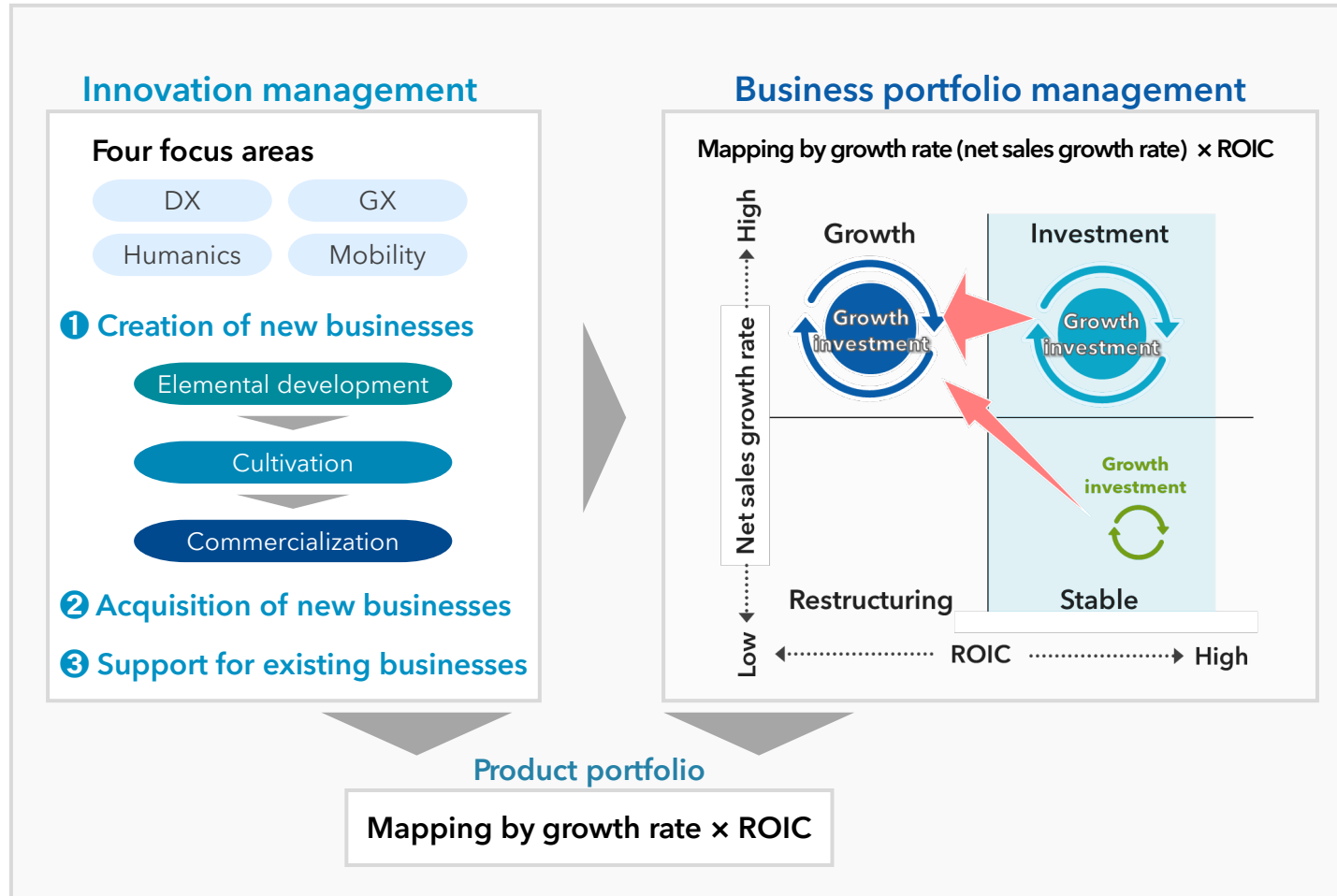
Dividend payout ratio:
30% or above

Other shareholder returns

Flexible share buybacks to be implemented depending on cash flows and the progress in growth investment

- Implemented share buybacks worth approx. ¥30bn in Feb-Apr. 2025

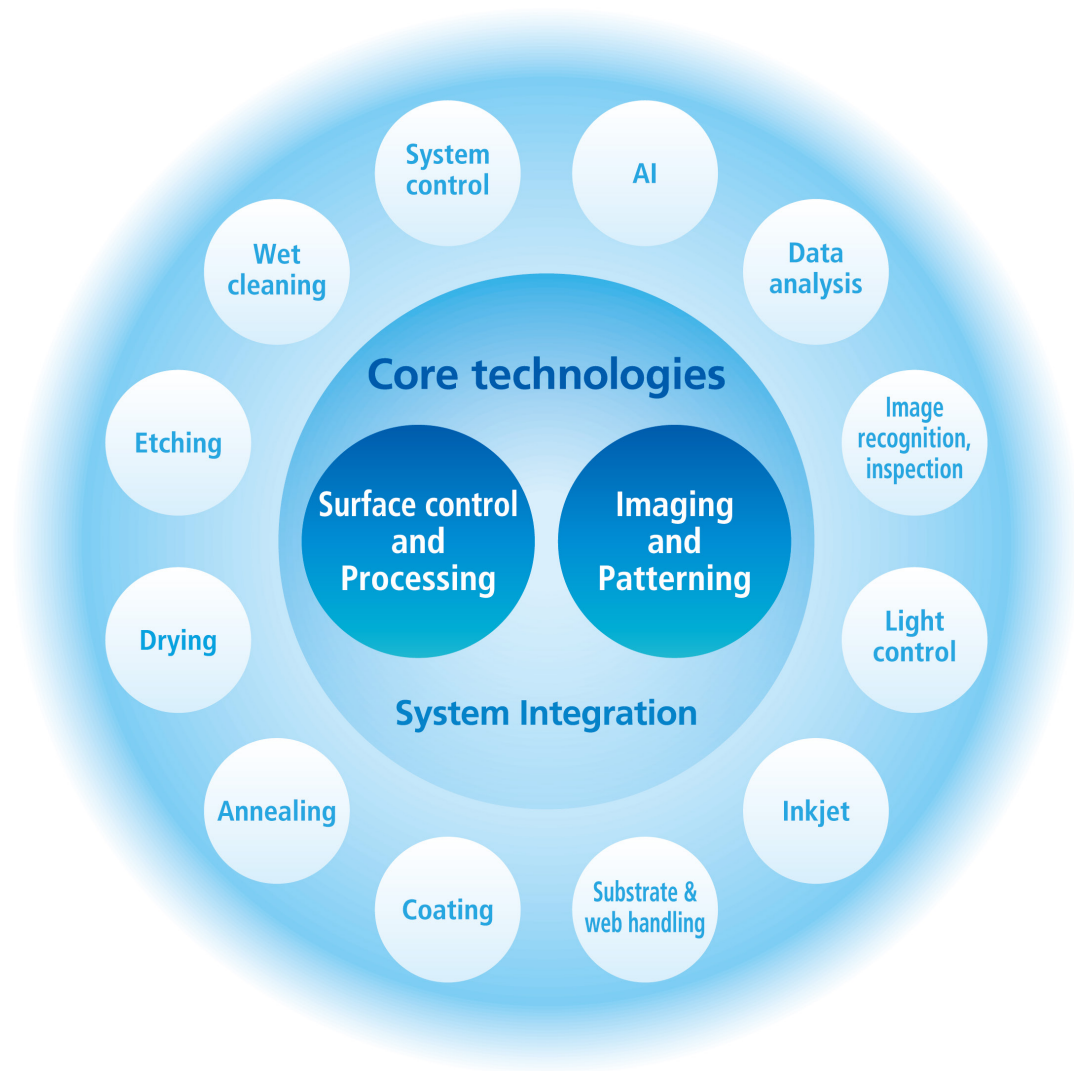
Value Up Further 2026: Portfolio management



- Revisiting the exit criteria applied to existing and new businesses
- Redefining our goals with respect to portfolio management with a forward-looking mindset, considering a variety of options, including M&A

Note: Portfolio management is done under the leadership and supervision of the holding company, with periodical reports made to and confirmed by the HD Board of Directors.

Core technologies redefined



Redefined our core technologies in line with the revised corporate philosophy

Core technologies:

Surface control and processing and **imaging and patterning**, combined through **system integration**

Elemental technologies:

Basic technologies derived from the core technologies are positioned around them like satellites

Value Up Further 2026: Progress toward the 3-yr financial targets

		Value Up Further 2026 (FY2025/03-FY2027/03) 3-yr cumulative targets	1st year results (FY2025/03)	2nd year forecasts (FY2026/03)	2-year cumulative forecasts
Consolidated	Cumulative sales	¥1.8 trillion or more	¥625.2 bn	¥621.0 bn	¥1,246.2 bn
	Average OP margin	19% or above	21.7%	18.8%	20.3%
	ROIC	15% or above	24.7%	19.6%	-
	Shareholder Returns	Consolidated dividend payout ratio:30% or above (Flexible share buybacks will be implemented depending on the progress of growth investment)	• Consolidated dividend payout ratio: 30.1% • Implemented share buybacks	Consolidated dividend payout ratio:30% or above (Flexible share buybacks will be implemented depending on the progress of growth investment)	Consolidated dividend payout ratio:30% or above (Flexible share buybacks will be implemented depending on the progress of growth investment)
SPE	Cumulative sales	¥1,500.0 bn or more	¥519.5 bn	¥502.0 bn	¥1,021.5 bn
	Average OP margin	23-25%	26.4%	24.1%	25.3%
GA	Cumulative sales	¥150.0 bn or more	¥53.0 bn	¥53.0 bn	¥106.0 bn
	Average OP margin	6-9%	8.1%	4.7%	6.4%
FT	Cumulative sales	¥100.0 bn or more	¥35.8 bn	¥45.5 bn	¥81.8 bn
	Average OP margin	3-5%	8.5%	17.4%	13.5%
PE	Cumulative sales	¥50.0 bn or more	¥14.1 bn	¥15.0 bn	¥29.1bn
	Average OP margin	12-15%	7.5%	6.7%	7.1%

Note: The above figures are predicated on organic growth.

Value Up Further 2026: Business growth strategy

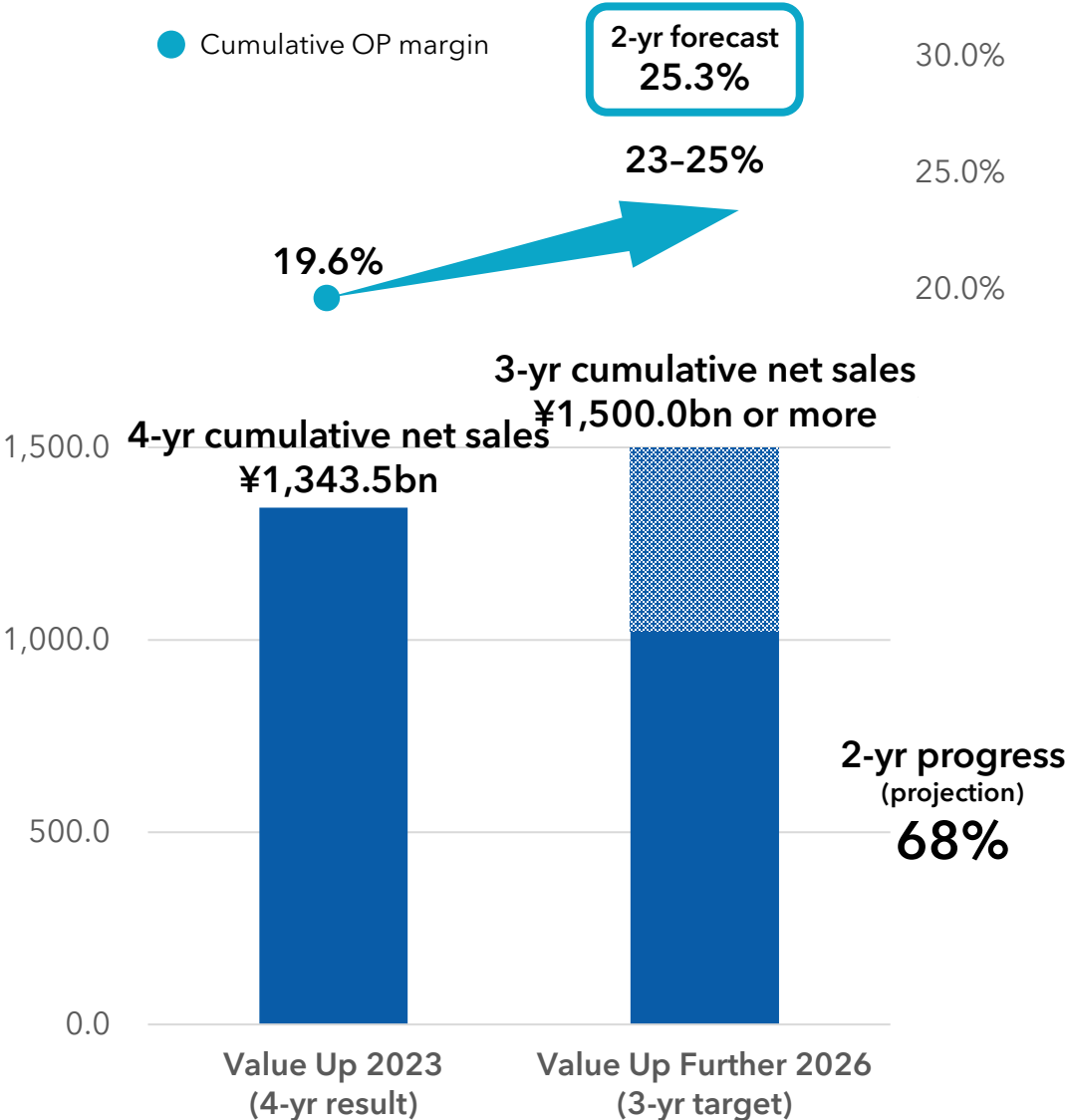
SPE

Main initiatives

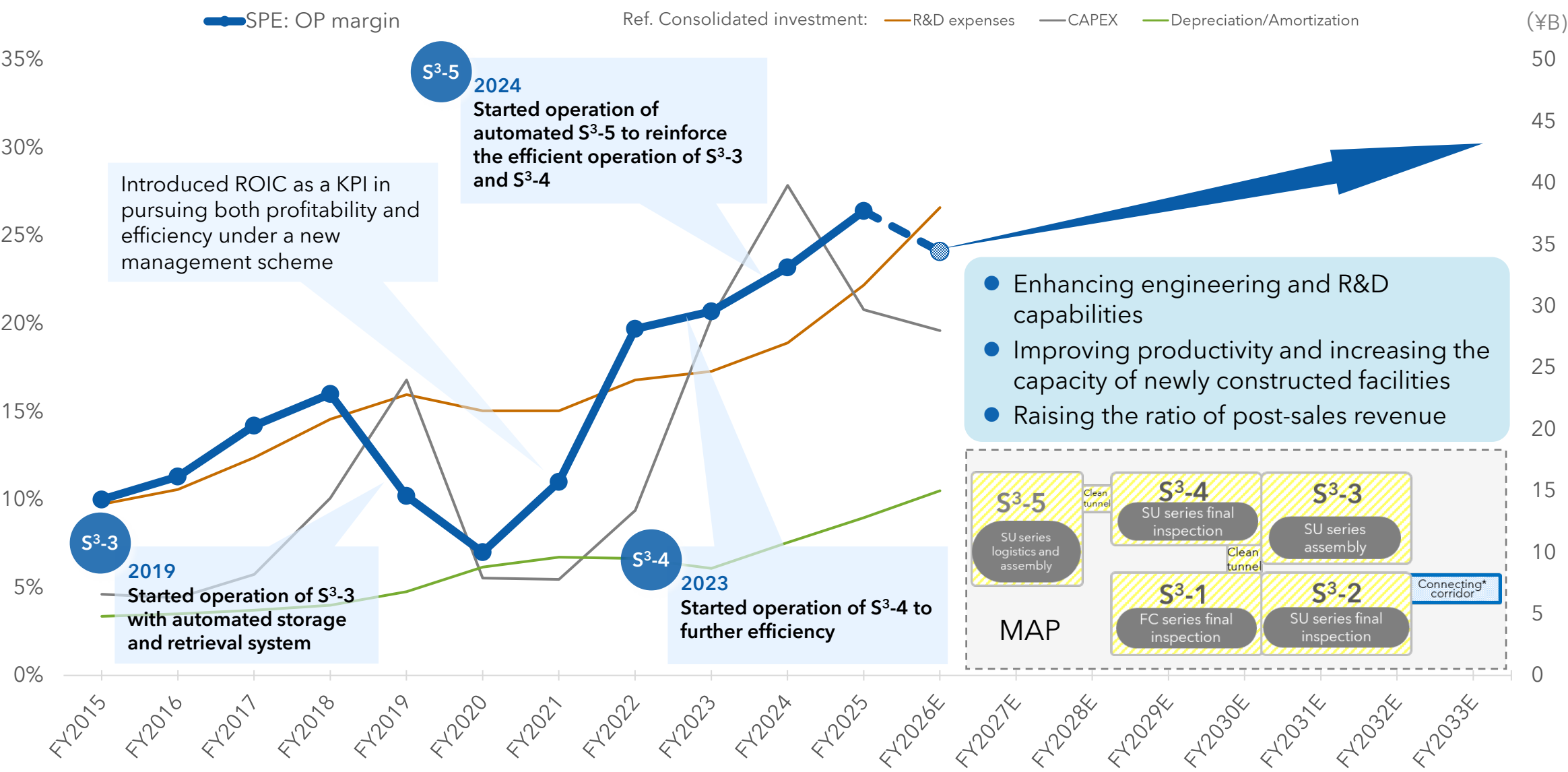
- 1. Improve the market share of the cleaning equipment
 - >> *Develop an optimal R&D environment* and *win new PoRs*
- 2. Expand the production capacity
 - >> Shorten the lead time by improving productivity, pursue automation
- 3. Enhance the business foundation
 - >> Streamline operation through DX
 - >> Recruit & nurture top talents

3-yr cumulative targets

Net sales	OP margin
¥1,500 bn or more	23% - 25%



Improving SPE profitability



Value Up Further 2026: Business growth strategy

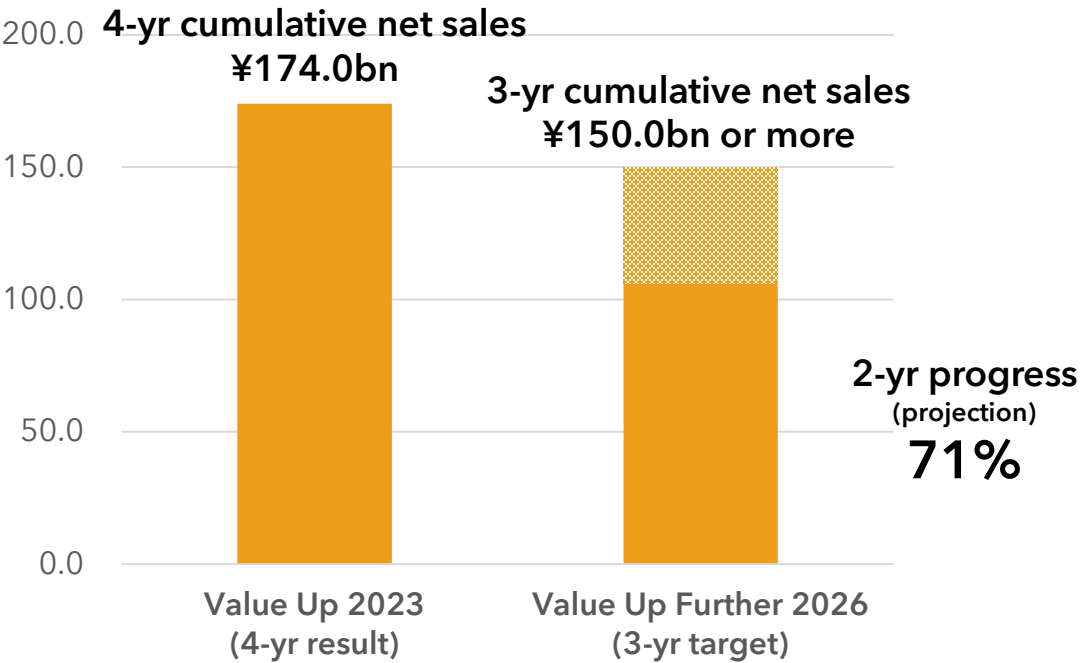
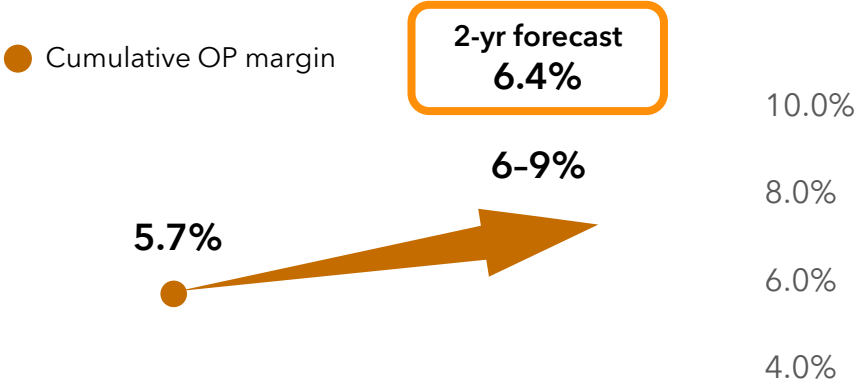
GA

Main initiatives

- 1. Expand the sales pipelines of POD equipment
>> Enhance our approach to large-order clients
- 2. Expand recurring business
>> Initiatives to improve the operation rate on the client side
- 3. Establish package printing business

3-yr cumulative targets

Net sales	OP margin
¥150 bn or more	6% - 9%



Value Up Further 2026: Business growth strategy

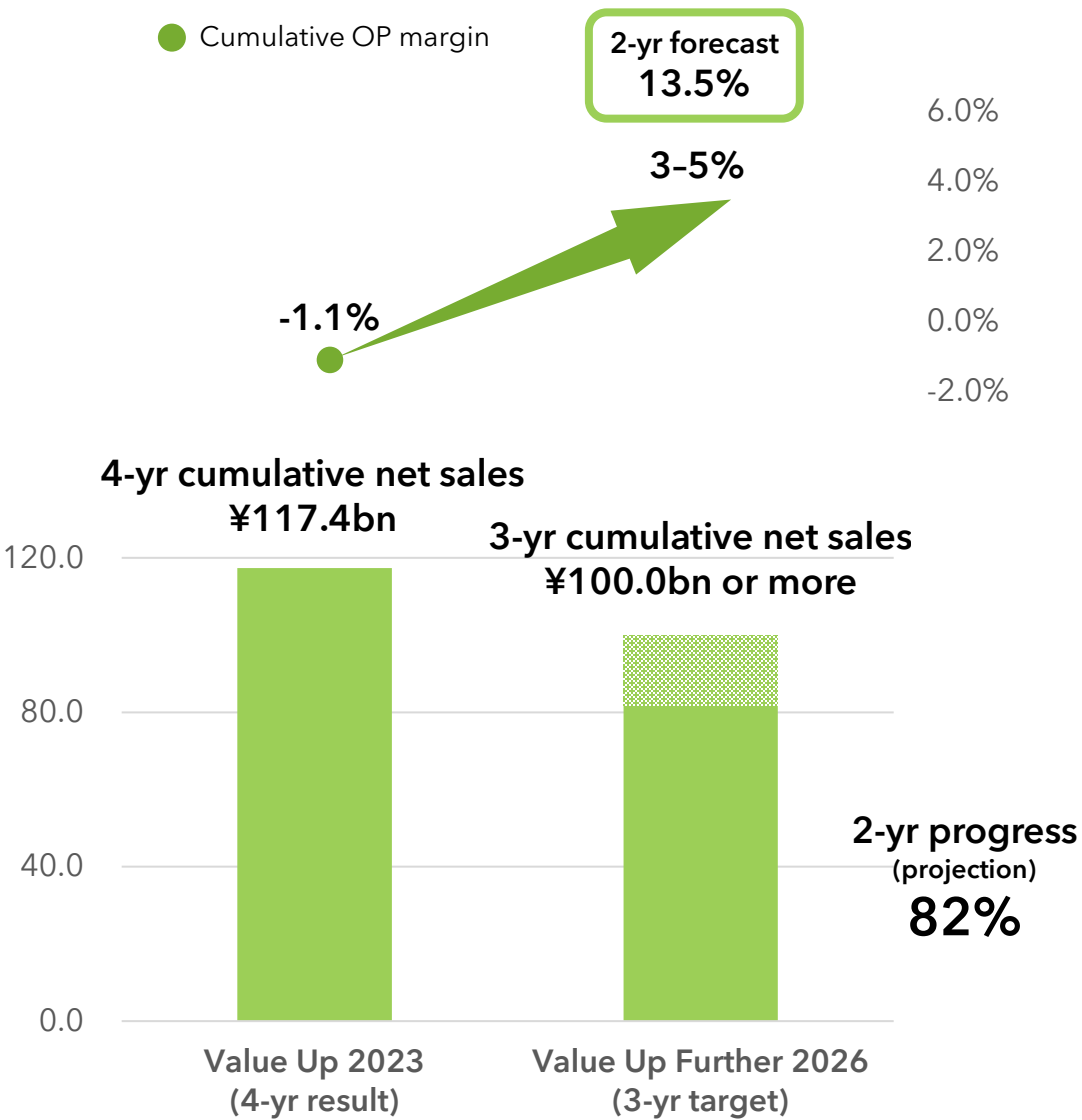
FT

Main initiatives

- 1. Improve the profitability of display business
- 2. Enhance our proprietary coating technique and expand the scope of its application
 - >> Enhance roll-to-roll products and technologies
- 3. Expand the scope of internal OEM business
 - >> ADPKG and hydrogen-related products

3-yr cumulative targets

Net sales	OP margin
¥100 bn or more	3% - 5%



Value Up Further 2026: Business growth strategy

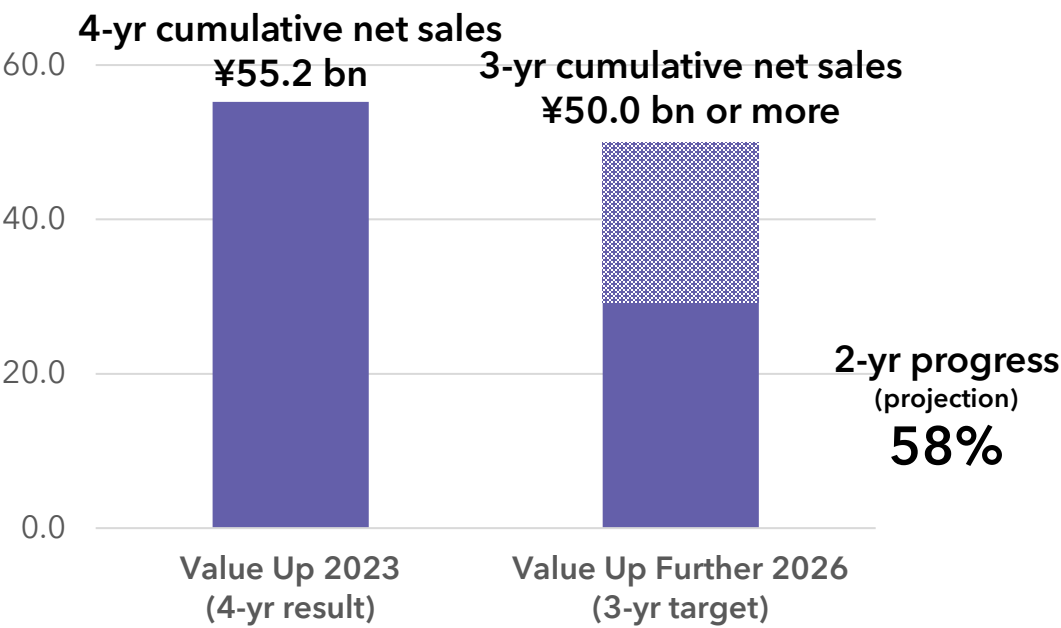
PE

Main initiatives

- 1. Enhance the presence of the direct patterning equipment in the industry
 - >> Increase our market share in direct lithography for solder resists (SR)
 - >> Launch direct patterning solutions for circuit pattern resists
- 2. Expand the use of direct patterning for different applications

3-yr cumulative targets

Net sales	OP margin
¥50 bn or more	12% - 15%



Business growth strategy: New business and innovation management

Creating new businesses that could eventually reach the level of our existing businesses as well as solutions that strengthen the existing businesses, focusing on the four areas based on megatrends we have identified.

Focus areas

DX

Contribute to DX
in society
DX in equipment

GX

Contribute to
decarbonization
Make low-energy
equipment

Humanics

Automation/
self-driving
Integrate people and
technologies

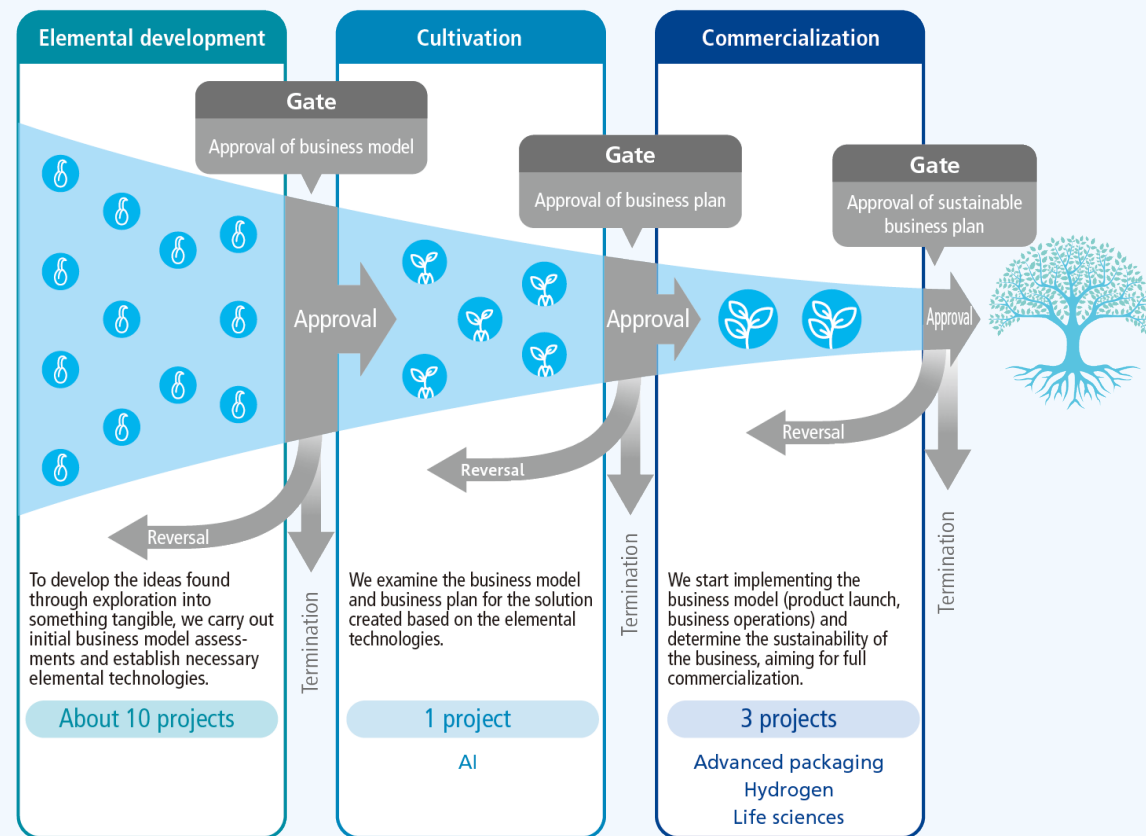
Mobility

Technologies that
support convenient
transportation of
people and goods

Exploration

① Creation of new businesses

We seek to create solutions with the potential to become new businesses and contribute to the growth envisioned in the Management Grand Design.



② Acquisition of new businesses

We seek to capture opportunities for collaboration with other companies (including investment, M&A, and other forms of capitalization), aiming to create new businesses and expand the existing business portfolio. Priority investment areas → SPE, advanced packaging, hydrogen energy, etc.

Main results of initiatives in the fiscal year ended March 31, 2025

- Added Kyo Diagnostics K.K., which develops next-generation cancer diagnostic support systems and services, to the Group as a subsidiary
- Added CGS ORIS GmbH, which develops and sells color technology products, to the Group

③ Support for existing businesses

We create solutions that strengthen the existing businesses over the long term.

Value Up Further 2026: Business growth strategy

New Business



Advanced packaging

- Increase the market presence of existing products (direct imaging, coaters)
- Launch new products (Cu-Cu low-temperature hybrid bonding, etc.)
- Become profitable in the final year

Main initiatives

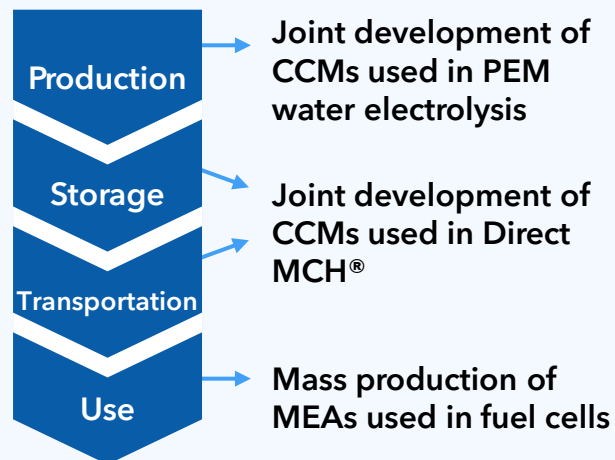
- **Direct imaging system:** LeVina
- **Coater for panels:** Lemotia
- **Low temperature hybrid bonding machine**



Hydrogen-related business

- Establish an OEM manufacturing framework for hydrogen MEAs
- Become profitable in the final year

Main initiatives



Life sciences

- Expand the sales channels of existing product
 - ➔ Reinforce cell inspection business
 - ➔ Step up sales of tablet inkjet printing equipment
- Establish a business model for personalized cancer treatment
- Promoting collaboration for Adriakaim to obtain medical certification

Main initiatives

- **Biosciences:** Cell inspection systems, etc.
- **Pharmaceuticals:** Tablet inkjet printing systems, etc.
- **Medical devices:** Medical devices for organ transplantation

Summary

1. Business portfolio is our top management priority

»» Realigning our business portfolio to gear it toward further growth, with emphasis on **growth potential** and **efficiency**

2. Allocating investment funds with focus on the growth areas

3. Our R&D, engineering, production, and marketing teams will continue to work together to further improve profitability

Committed to showing our stakeholders a solid track record of growth to maximize shareholder returns.

SPE: Wet etching and cleaning trends

SCREEN Semiconductor Solutions Co., Ltd.

Hiroaki Takahashi

Managing Director,
Head of R&D Strategy Operations



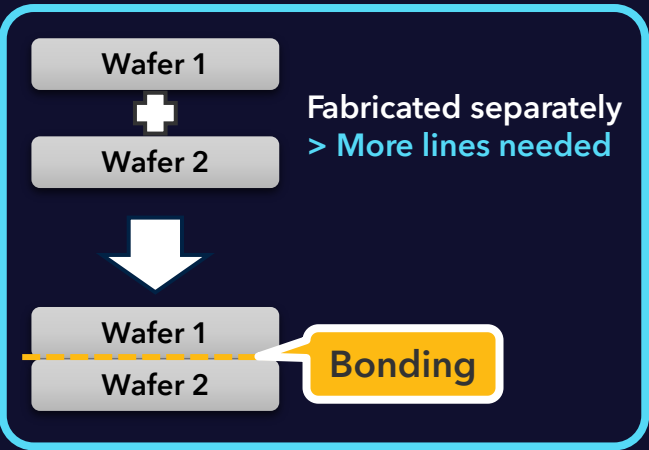
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Scaling x 3D integration

BSPDN: Back Side Power Delivery Network
CAR: Chemical Amplifier Resist
CFET: Complementary Field Effect Transistor
MOR: Metal Oxide Resist

“Miniaturization + **Bonding**” is becoming the mainstream in line with the evolving device architecture.

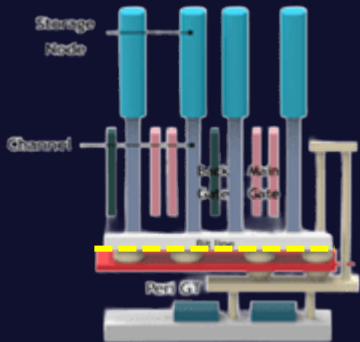


Logic BSPDN



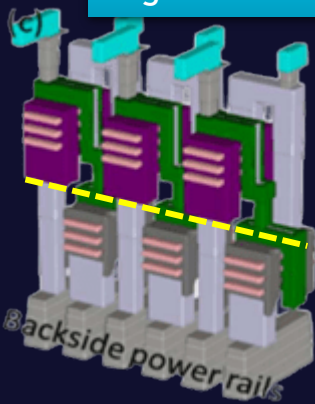
Source: intel, VLSI 2023

DRAM 4F2 VCT

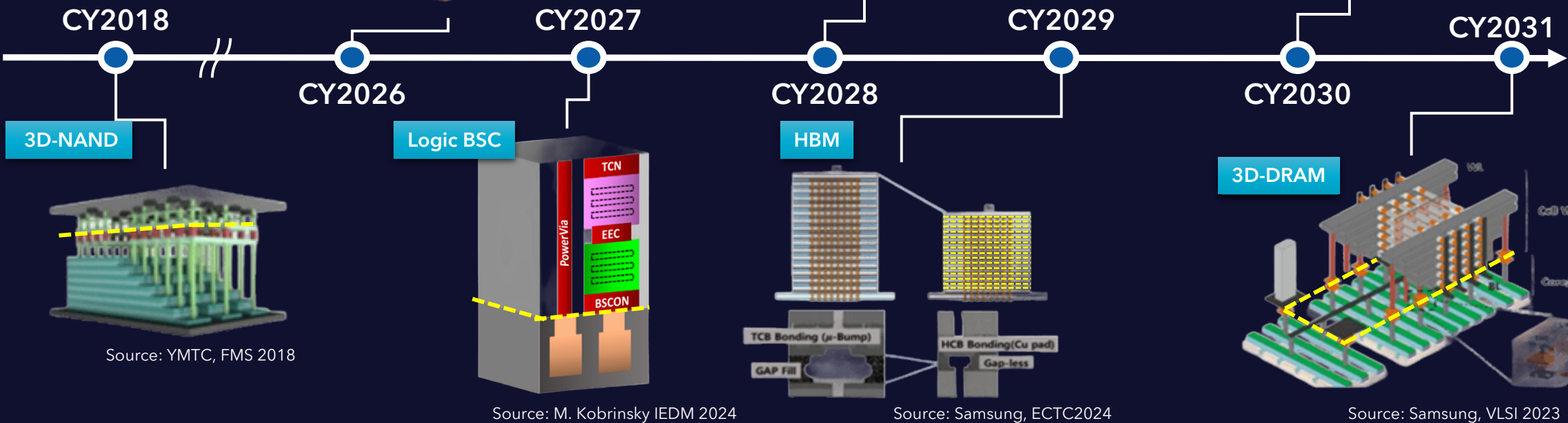


Source: SK hynix, VLSI2024

Logic Nanostack



Source: IBM, VLSI2025

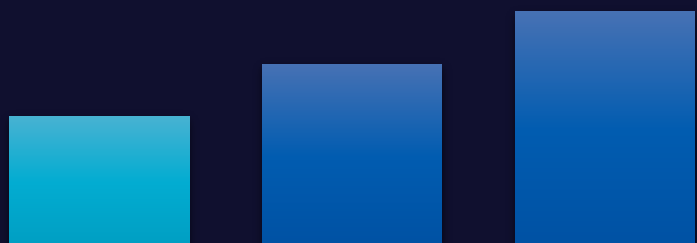


Expected increase in device processing steps, by structure

(SCREEN's estimates)

Logic

- Transistor structure: FF > NS > CFET
- Back-side wiring through bonding: Post-A16
- Transistor formation through bonding: sCFET



FF
Gen. X

Nanosheet
Gen. X+2

sCFET
Gen. X+5

FF: FinFET
NS: Nanosheet
sCFET: sequential Complementary Field-Effect Transistor

DRAM

- Memory cell structure: 6F2 > 4F2
- CMOS/Memory cell bonding: 4F2



6F2
Gen. X

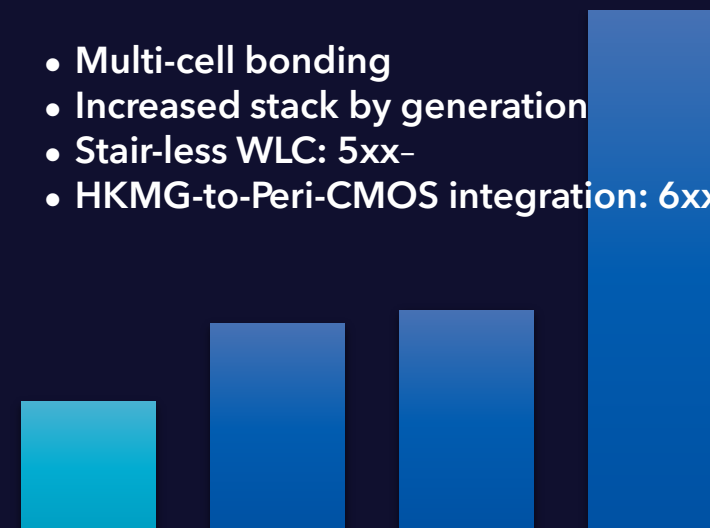
4F2(VCT)
Gen. X+3

VCT: Vertical Channel Transistor

*3D-DRAM under examination

NAND

- Multi-cell bonding
- Increased stack by generation
- Stair-less WLC: 5xx-
- HKMG-to-Peri-CMOS integration: 6xx-



CNA
Gen. X

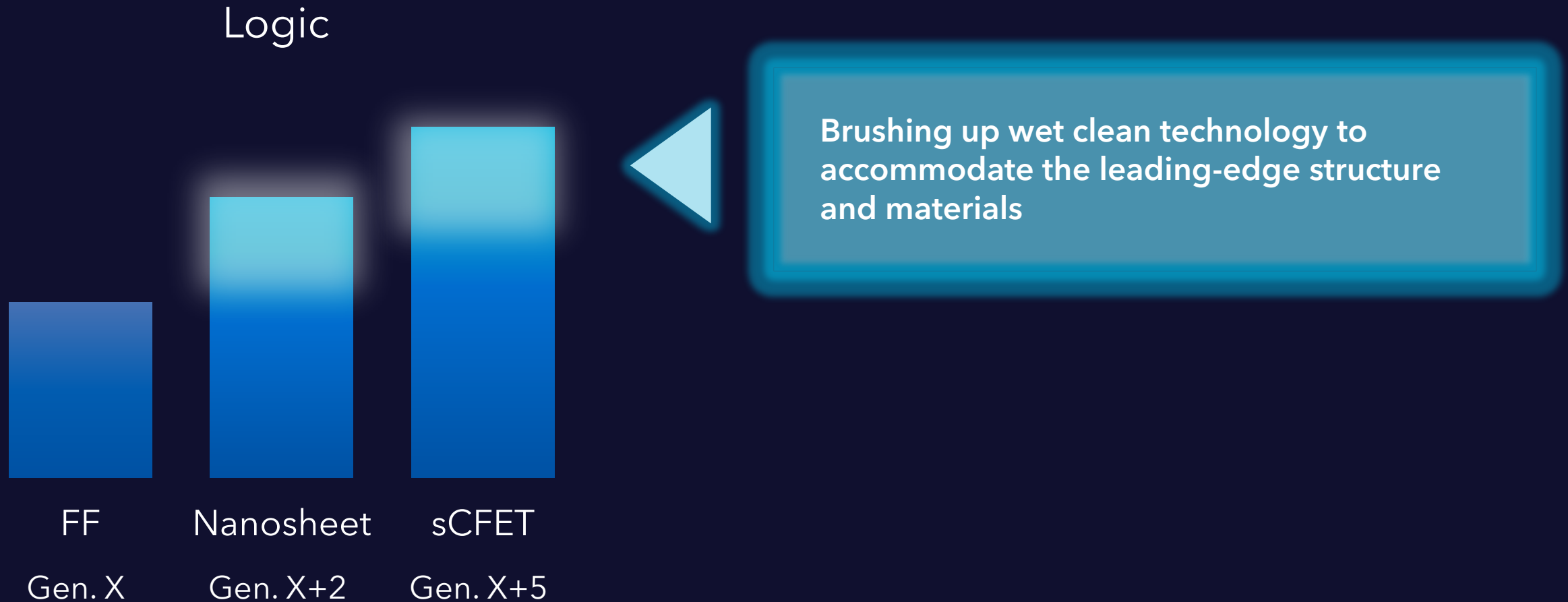
CUA
Gen. X+1

CBA
Gen. X+2

CBMA
Gen. X+5

CNA: CMOS Near to Array
CUA: CMOS Under Array
CBA: CMOS Bonded to Array
CBMA: CMOS Bonded to Multi-Array

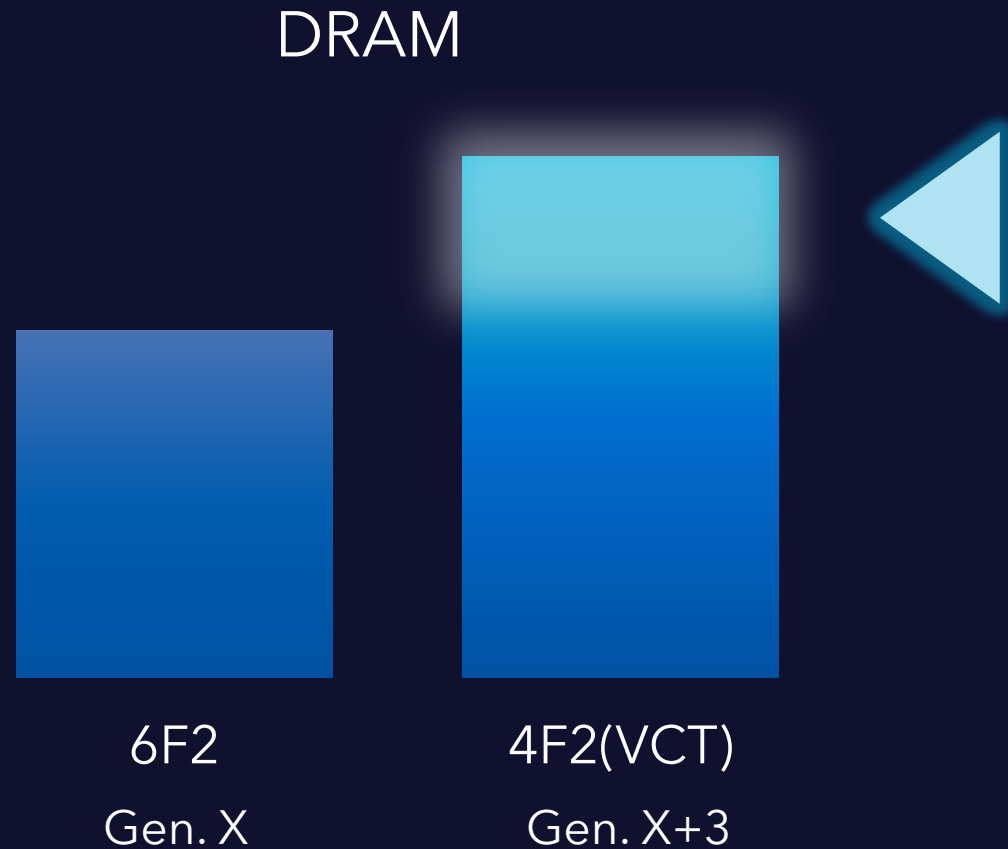
Expected increase in SCREEN SPE's sales: Logic



FF: FinFET

sCFET: sequential Complementary Field-Effect Transistor

Expected increase in SCREEN SPE's sales: DRAM



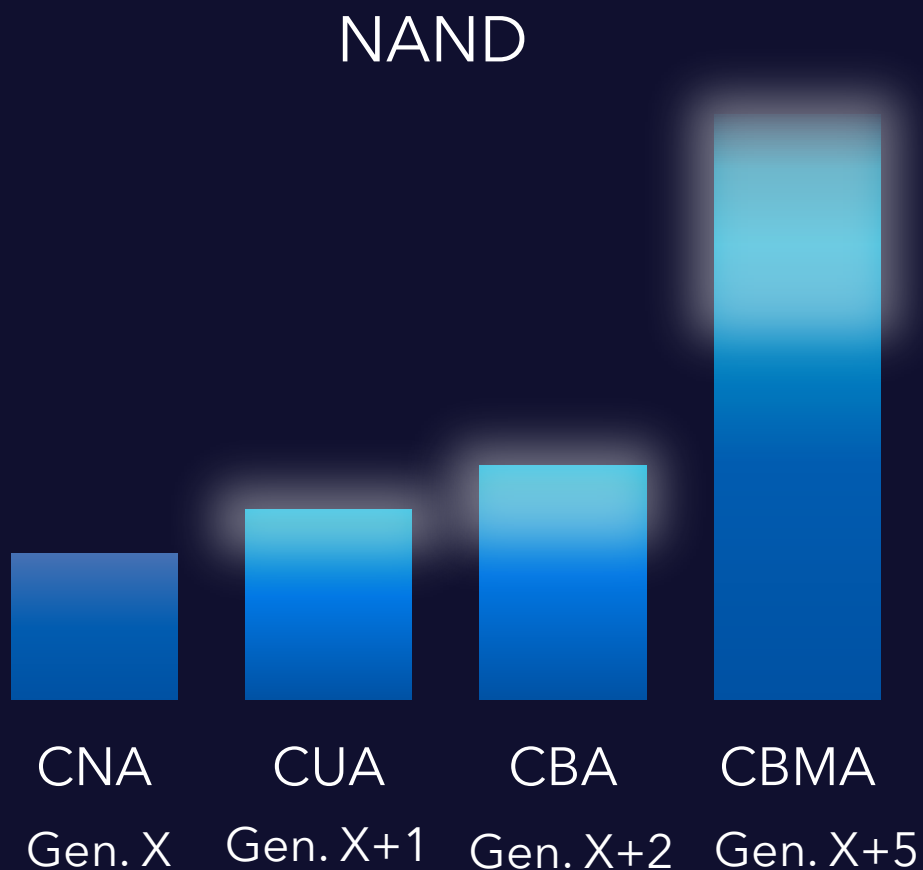
Expanding cleaning opportunities with Logic technology introduced in DRAM, and 3D packaging

Boosting market share by winning new PORs in DRAM by leveraging our Logic expertise

VCT: Vertical Channel Transistor

*3D-DRAM under examination

Expected increase in SCREEN SPE's sales: NAND



Expanding cleaning opportunities with Logic technology introduced in NAND, and 3D packaging

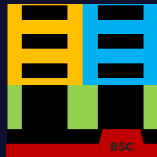
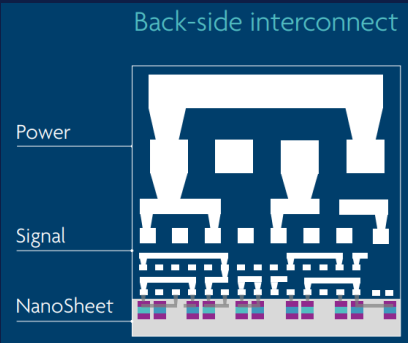
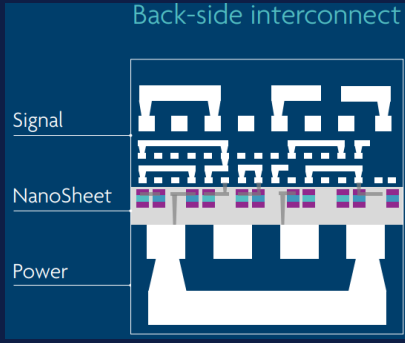
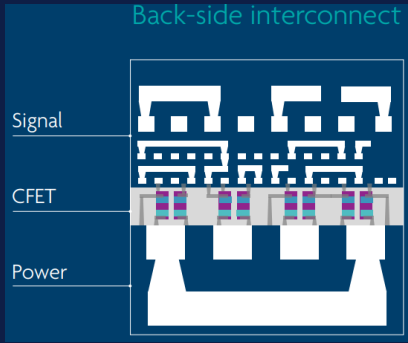
Process switch from batch cleaning to single-wafer cleaning with HKMG integration

Boosting market share by winning new PORs in NAND by leveraging our Logic expertise

CNA: CMOS Near to Array
CUA: CMOS Under Array
CBA: CMOS Bonded to Array
CBMA: CMOS Bonded to Multi-Array

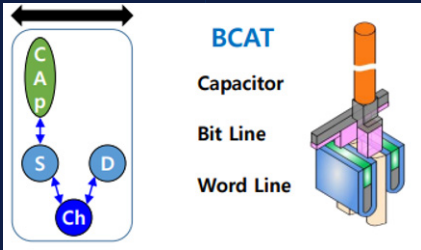
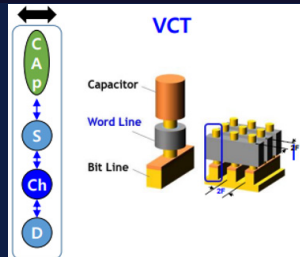
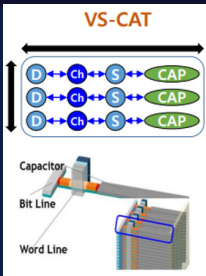
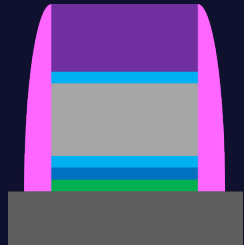
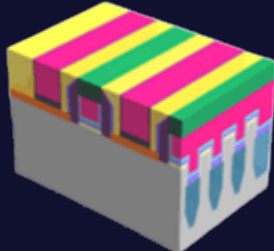
Logic roadmap

BSPDN: Back Side Power Delivery Network
CAR: Chemical Amplifier Resist
CFET: Complementary Field Effect Transistor
MOR: Metal Oxide Resist

CY	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
HVM Gen.	N3		N2		A16/A14		A10		A7		
Transistor											
EUV	NA=0.33				NA=0.33, NA=0.55				NA=0.55		
Resist	CAR		CAR		CAR, MOR		CAR, MOR		CAR, MOR		
Metal pitch [nm]	23nm		22nm		21nm		18nm		17nm		
Minimum defect	11.5nm		11nm		10.5nm		9nm		8.5nm		
BSPDN	 Back-side interconnect  Source: imec, ITF JAPAN 2024 Back-side interconnect  Source: imec, ITF JAPAN 2024 Back-side interconnect  Source: imec, ITF JAPAN 2024										

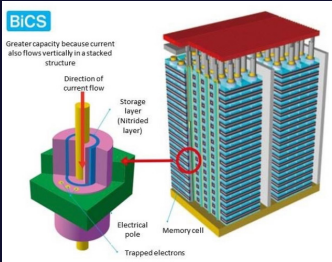
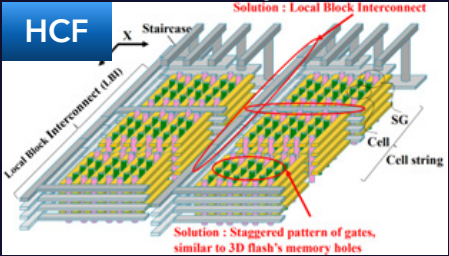
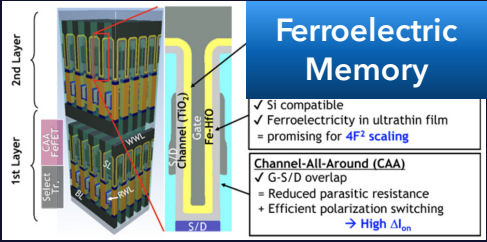
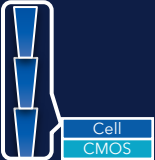
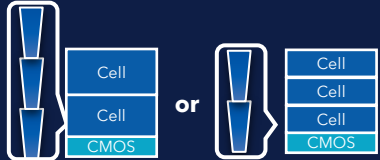
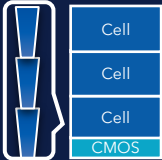
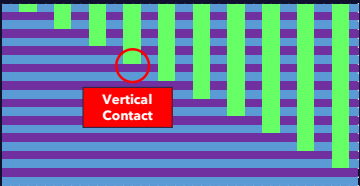
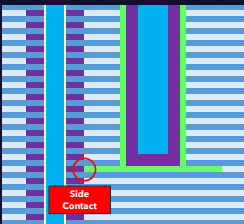
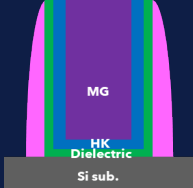
DRAM roadmap

BCAT: Buried Channel Array Transistor
 CAR: Chemical Amplifier Resist
 CBA: CMOS Bonded to Array
 CNA: CMOS Near to Array
 HKMG: High-k Metal Gate
 MOR: Metal Oxide Resist
 VCT: Vertical Channel Transistor
 VS-CAT: Vertically Stacked Cell Array Transistor

CY	23	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	
Gen. (1.5year/cycle)		D1B	D1C		D1D		D0A	D0B	D0C or 3D		D0D or 3D	
Cell layout		6F2	6F2		6F2		4F2	4F2	4F2 or 3D		3D	
		 Source: Samsung, IMW2024					 Source: Samsung, IMW2024				 Source: Samsung, IMW2024	
CMOS layout		CNA	CNA		CNA		CBA	CBA	CBA		CBA	
												
EUV		NA=0.33					NA=0.33, NA=0.55 (for Planar) , No process (for 3D-DRAM)					
EUV resist		CAR / MOR	CAR / MOR		CAR / MOR		CAR / MOR	CAR / MOR	CAR / MOR		CAR / MOR	
		HKMG (Gate First)	HKMG (Gate First)		HKMG (Gate First)		HKMG FinFET	FinFET	FinFET		FinFET	
Peri-CMOS											Source : SK hynix, VLSI2025	

NAND roadmap

CBA: CMOS Bonded to Array
CUA: CMOS Under Array
eWLC: exponential Word Line Contact
HCF: Horizontal Channel Flash
HKMG: High-k Metal Gate
VC: Vertical contact

	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Layer	2yy/3xx L		4xx L		6xx L		8xx L		10xx L	
Structure	 Source: Kioxia				Alternative memory structure  Source: Kioxia, IEDM2024		Alternative memory scheme  Source: Kioxia, VLSI2023			
Stack image	CUA / CBA 		CBA 		CBA 		CBA 		CBA 	
WLC	VC 		VC 		eWLC 		eWLC 		eWLC 	
CMOS	PolySi 		PolySi 		HKMG (Gate Last) 		HKMG (Gate Last) 		HKMG (Gate Last) 	

Single-wafer cleaning for evolving DRAM and NAND processes

- Combining wafer cleaning and wet etching expertise, accommodating a range of device architecture, production, and processes, built over a half century.
- Accommodates wide-ranged evaluation during the development phase and smooth narrowing during the large-scale production phase.

Proven track records

- No.1 market share in single-wafer cleaning
- Supporting advanced Logic miniaturization
- Driving improvements in device yield

Features

- Multi-process chambers for loading several types of chemicals
 - Acid, alkali, and organic chemicals can be loaded at the same time
 - Allows to reclaim and reuse several types of chemicals
 - Flexible chemical combinations possible with DDI*
- *DDI: Dynamic Direct Injection

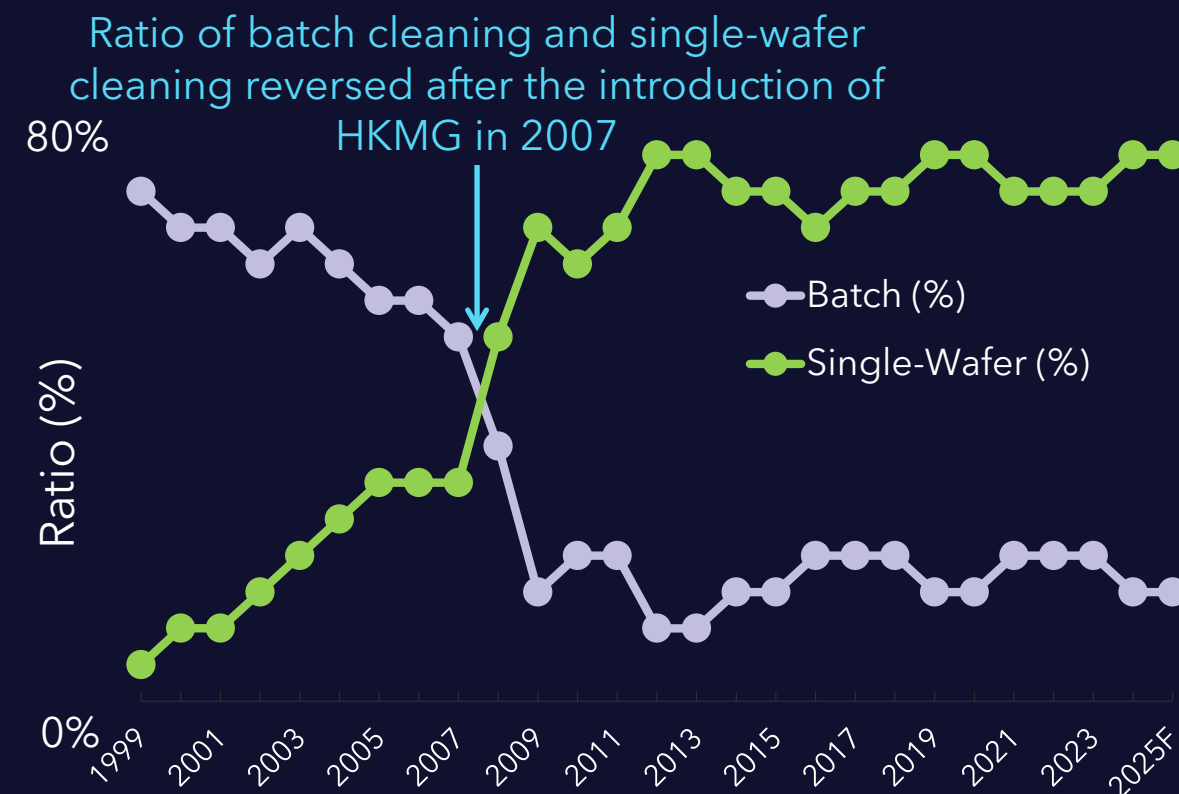
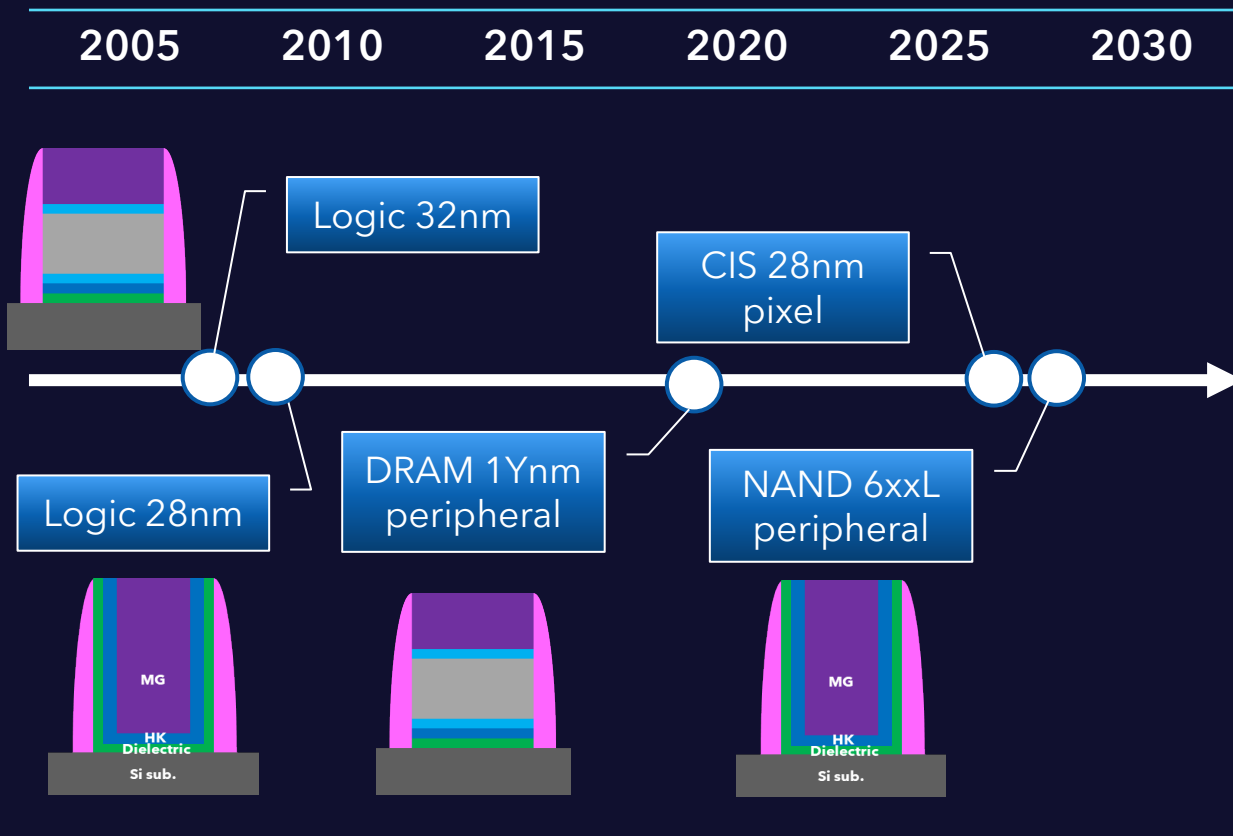


Process applications

- HF, APM, HPM, etc. (mainly for particle removal)
 - ✓ Pre-deposition clean, post-deposition/dry clean
- SPM (mainly for resist, organic residue, and slurry removal)
 - ✓ Resist removal
 - ✓ Post-process clean (DRY, CMP)
- Wet etching (mainly for processing)
 - ✓ Metal etch
 - ✓ Oxide film etch
 - ✓ Si etch

Single-wafer cleaning more in demand with HKMG integration

- HKMG-CMOS is increasingly adopted to accommodate the need for high-speed, energy-saving devices, in step with the AI revolution.
- Demand for single-wafer wet cleaning will increase further.

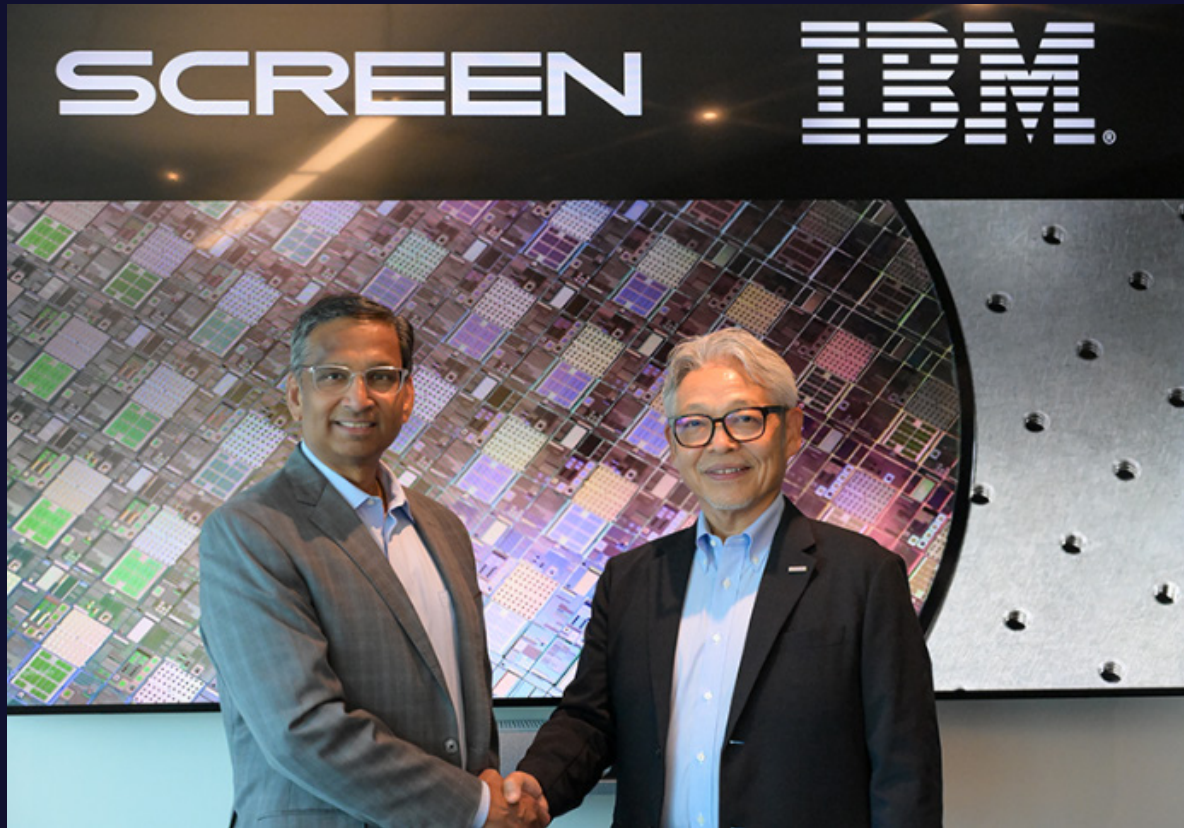


Source: Created based on Gartner data

Single-wafer wet cleaning are better suited to prevent cross contamination.

Joint R&D with IBM

Press release published September 24, 2025: *SCREEN and IBM Sign Agreement for Next-Generation EUV Lithography Cleaning Process Development - Agreement builds on more than a decade of collaboration between the two companies*



Left:

**Dr. Mukesh Khare, GM of IBM Semiconductors and
VP of Hybrid Cloud, IBM**

Right:

**Akihiko Okamoto, Representative Director and
President of SCREEN Semiconductor Solutions**

Off-shore R&D base, "ATCA," established in New York

Press release published December 16, 2025: *SCREEN to establish an R&D center in Albany, New York for semiconductor production processes*



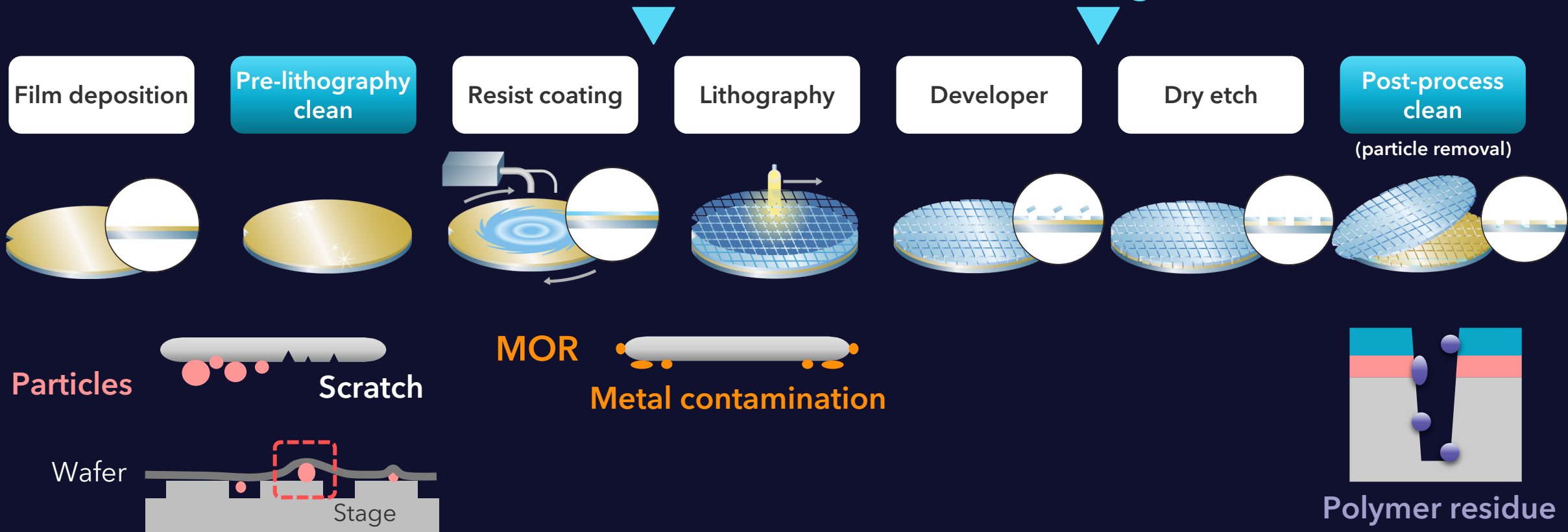
ATCA will be located within Albany NanoTech Complex, the state-of-the-art semiconductor facility operated by NY Creates (NYCR).

It will be using NYCR's clean room and other infrastructure to pursue solo research as well as joint research with global partners.

We will aim to increase our presence in wet cleans as well as thermal processing and advanced packaging.

Back-side and bevel cleaning: Growing importance in the EUV process flow

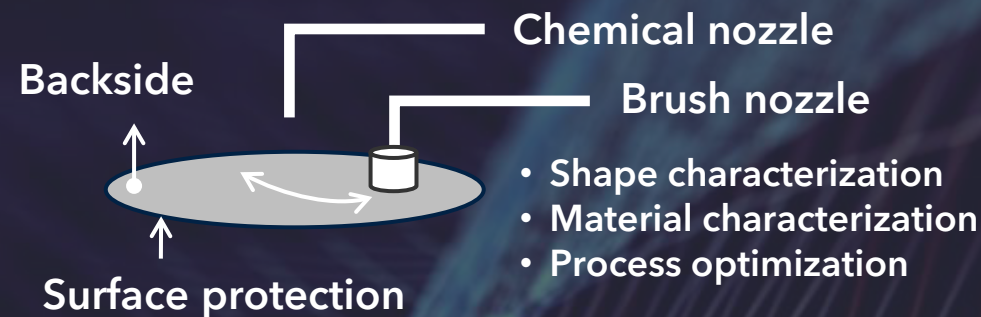
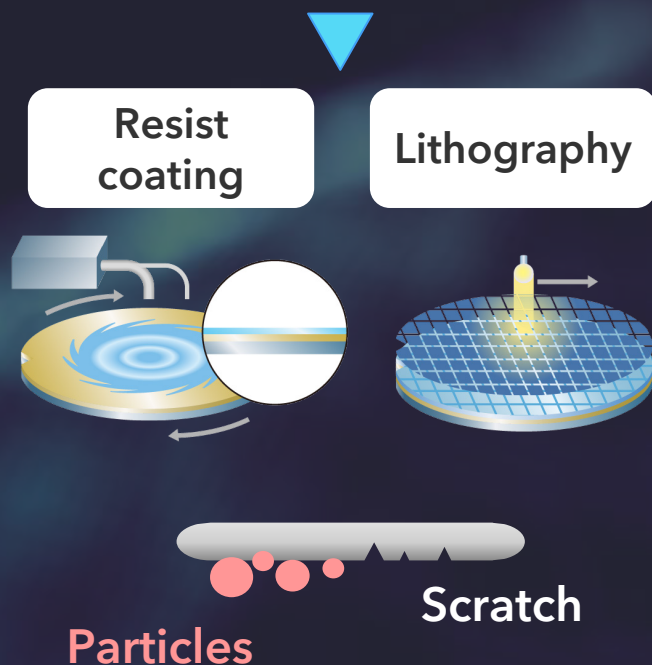
Back-side and bevel cleaning



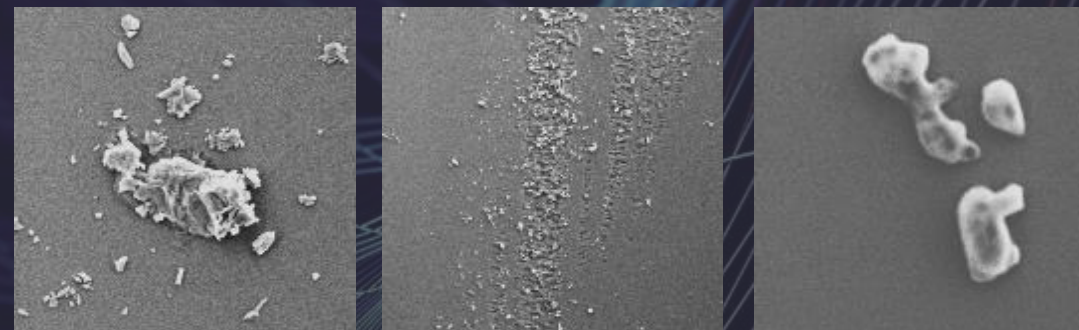
Back-side cleaning to maximize patterning performance

Combining chemical and physical cleaning for optimal back-side processing

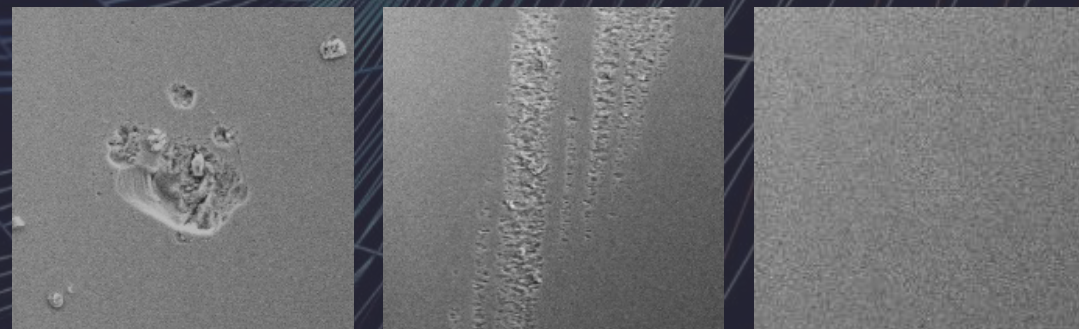
Back-side and bevel cleaning



Before



After



Wafer bonding process

Pre-bonding

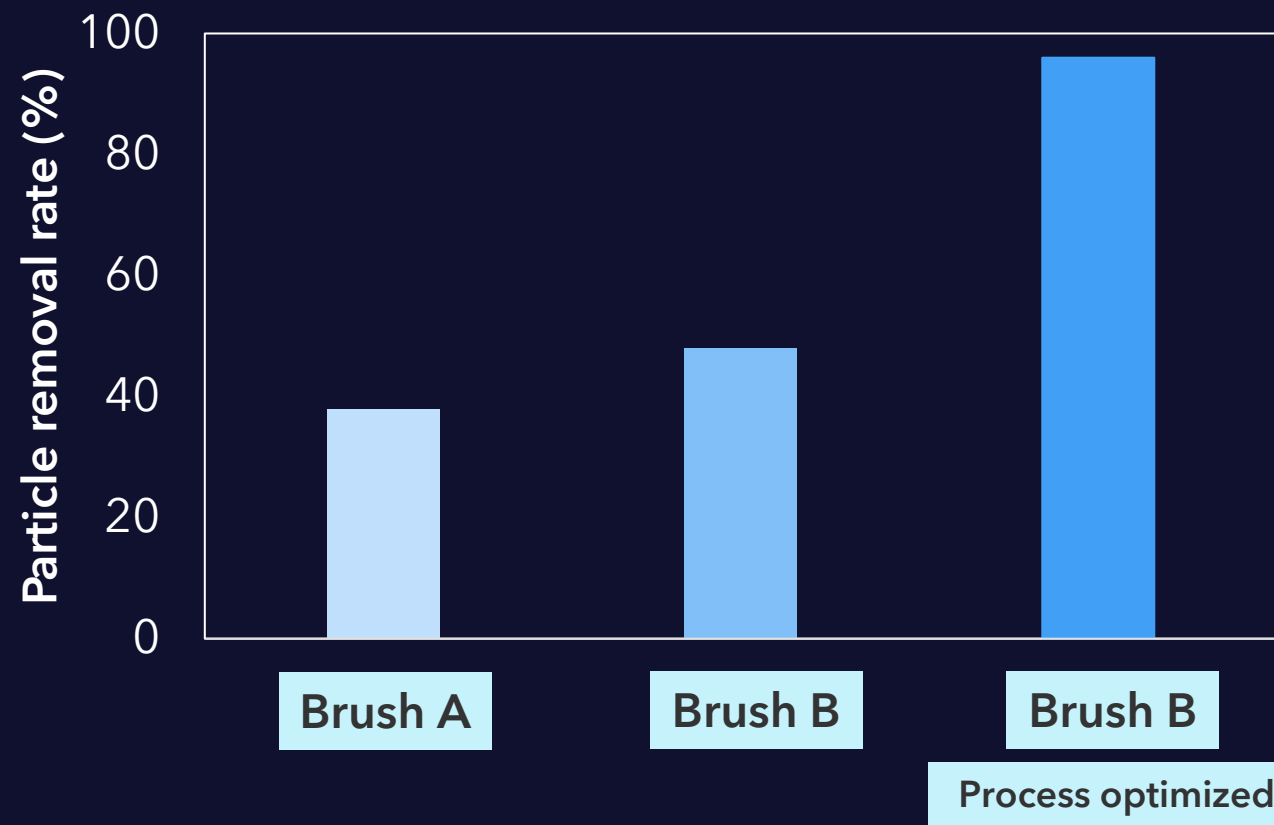
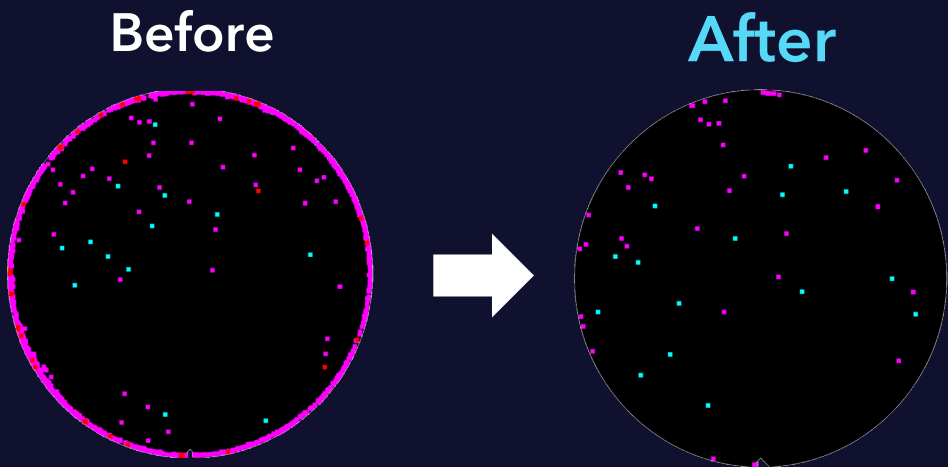
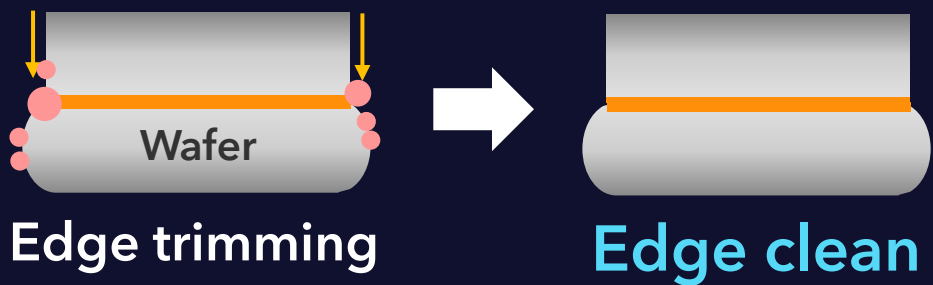


Post-bonding



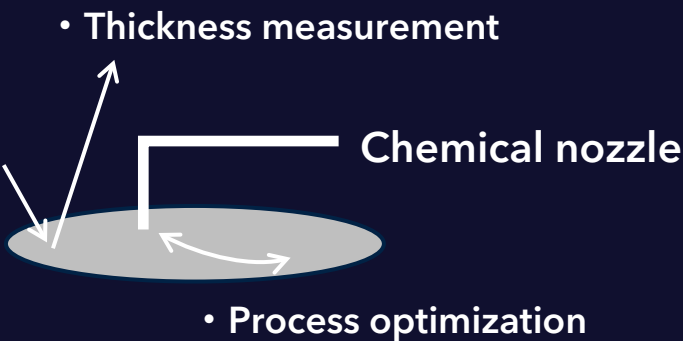
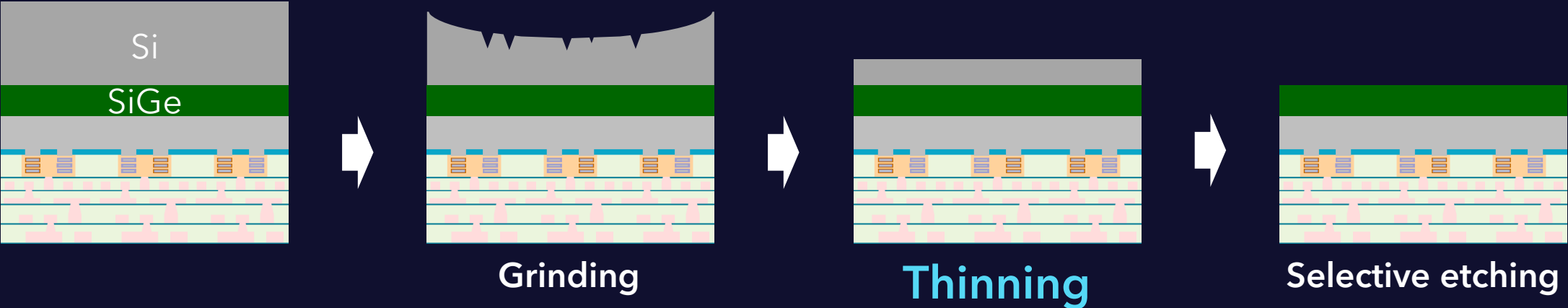
Edge clean after wafer trimming

Brush cleaning to remove particles on wafer edges

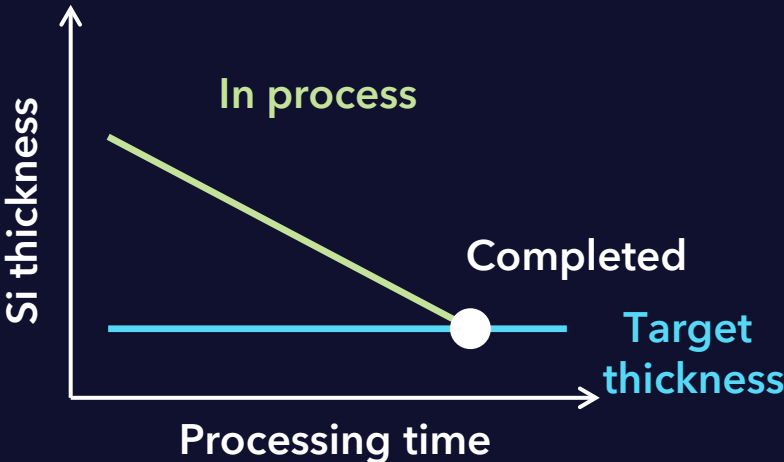


Wafer thinning after bonding

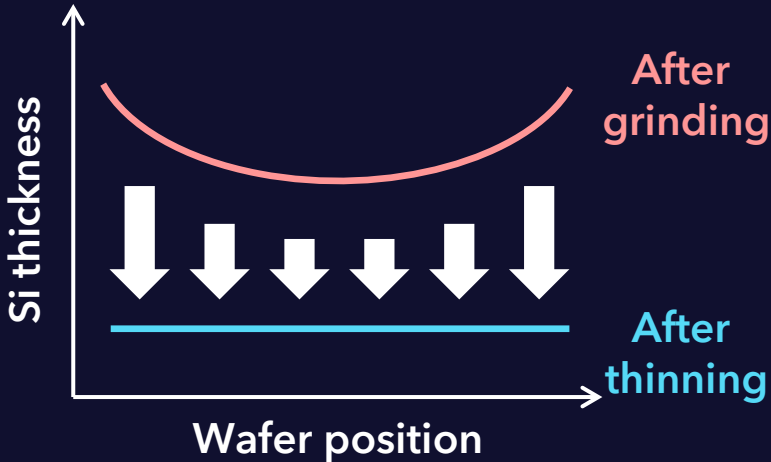
Leveraging wet etching expertise and etching profile adjustment knowhow



Wet etching

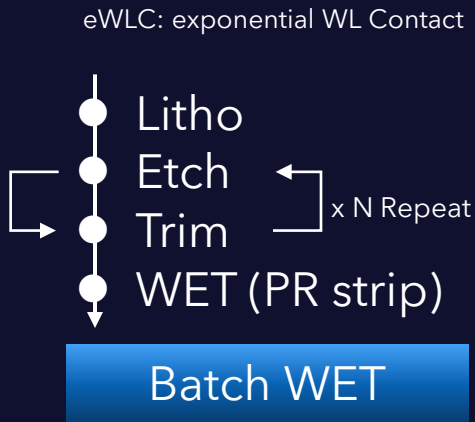
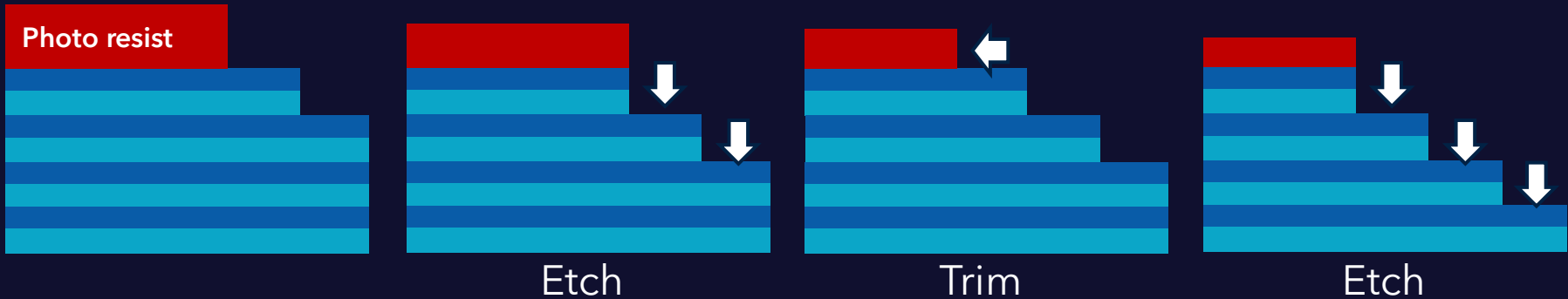


Etching profile adjustment



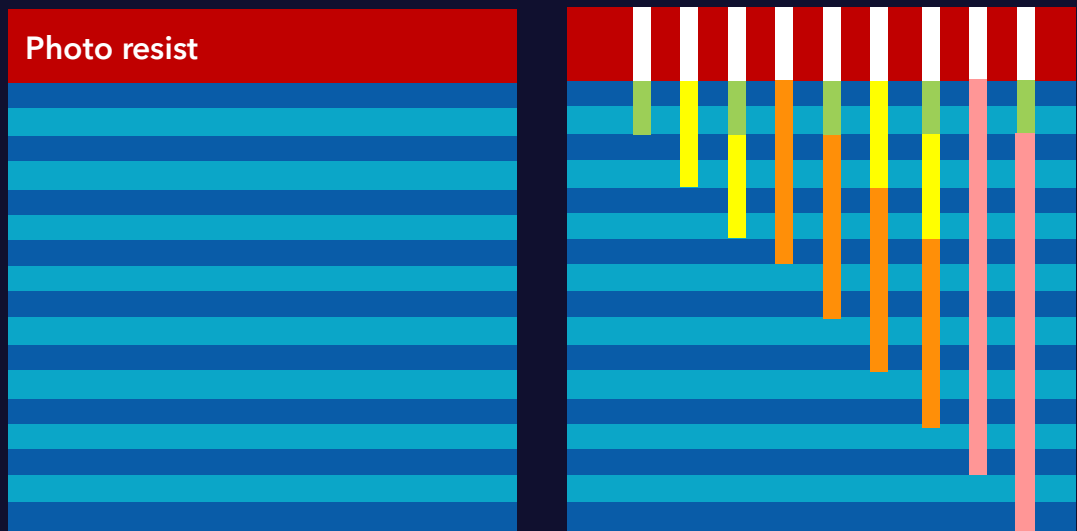
Single-wafer SPM more in demand with NAND eWLC process

● Conventional Process (w/ staircase)



● eWLC process (w/o staircase)

* Estimated based on TechInsights data



# of etch	Etched layer
1	$2^0=1$
2	$2^1=2$
3	$2^2=4$
4	$2^3=8$

●

●

●



Potential challenges

- Selectivity for stacking material
- PR removal
- SPM chemical reduction
- SPM drain cost

More opportunities to leverage our experience working with foundries

Summary

*Aiming for further growth in wet cleaning
leveraging our technological excellence*

HKMG

**High-NA
EUV**

**Wafer
Bonding**

**Novel
Structure**

New material

New architecture

A Better Tomorrow With Our Partners



Advanced packaging trends and outlook

SCREEN Semiconductor Solutions Co., Ltd.

Joichi Nishimura

General Manager, Engineering and Marketing
Advanced Package Department (ADPKG)



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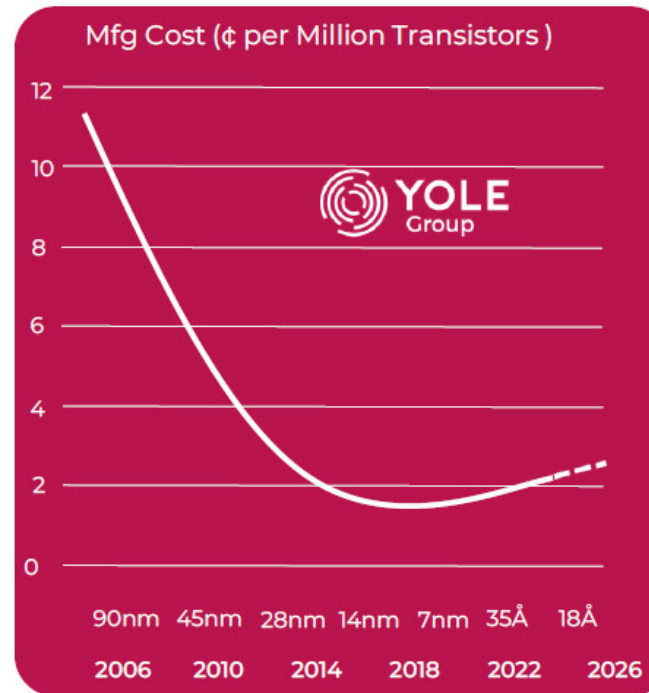
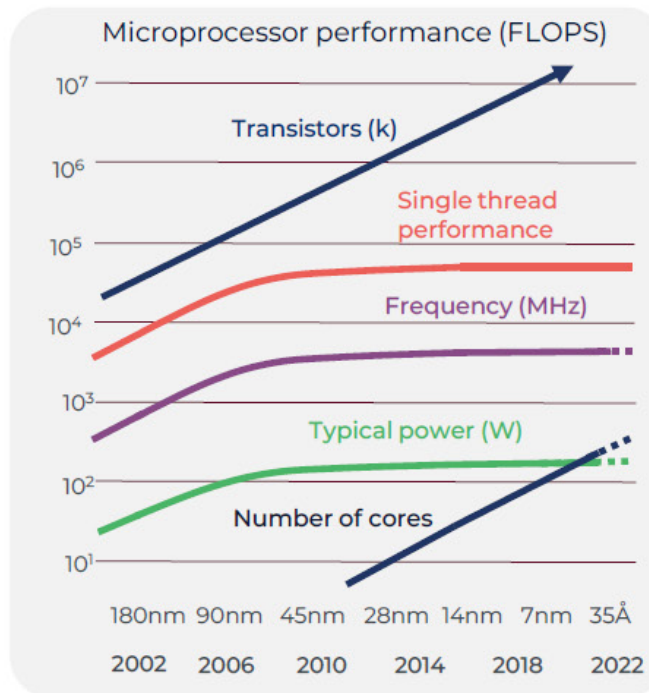
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Why is advanced packaging important?

Challenges:

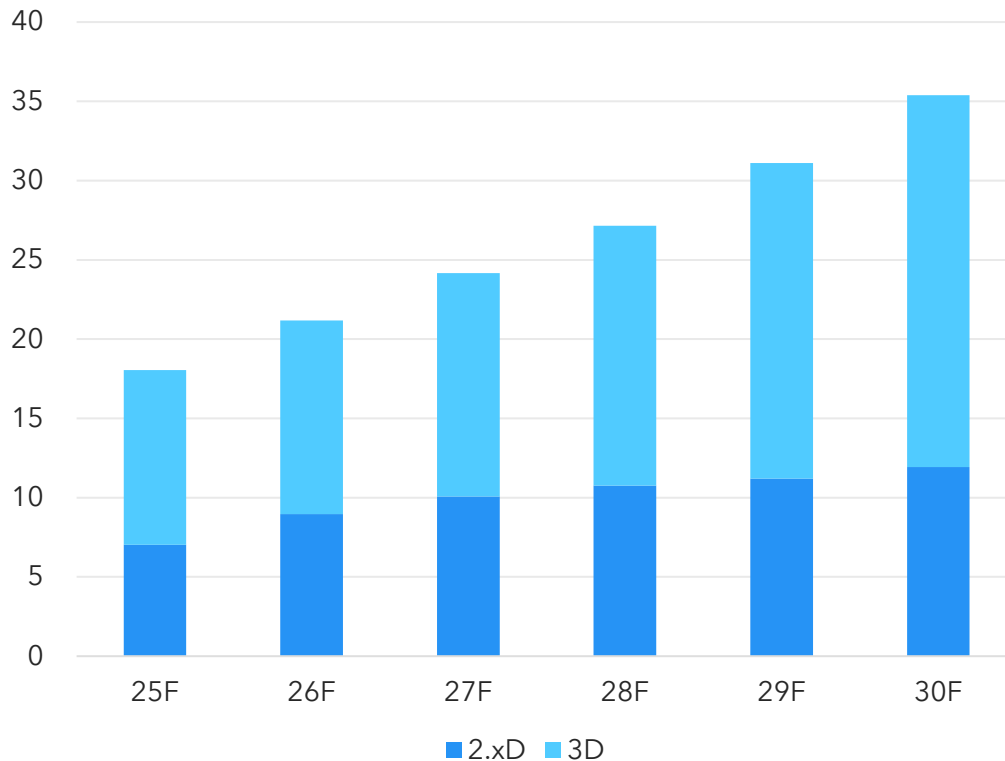
- The slowdown of Moore's Law
- While miniaturization has increased transistor density, performance gains have plateaued, and power consumption continues to rise.
- The reduction in manufacturing costs has already reached its limit, while design costs continue to rise.

To overcome these challenges, leveraging advanced packaging technologies has become essential.



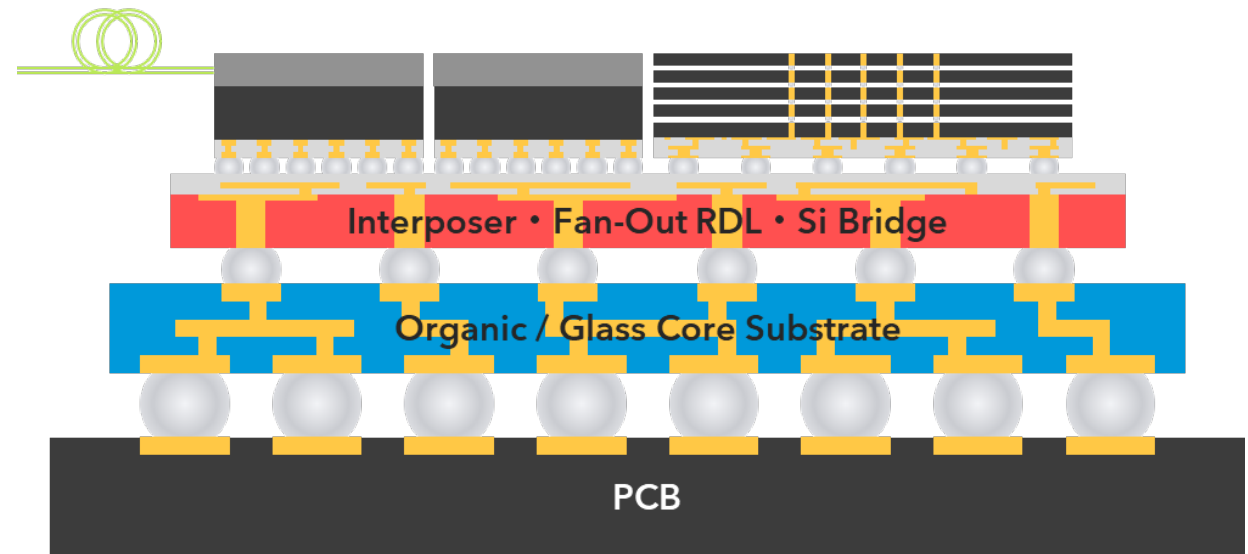
2.xD and 3D packaging: market trends and key focus areas

2.xD / 3D packaging market forecast, \$Bn



Data from Advanced Packaging Market Monitor, Q2 2025 - Yole Group

The 2.xD and 3D packaging markets are expected to maintain strong growth momentum.



Key focus areas:

- 3D packaging solutions: development (WoW bonding system, etc.)
- 2.xD packaging solutions: development and marketing

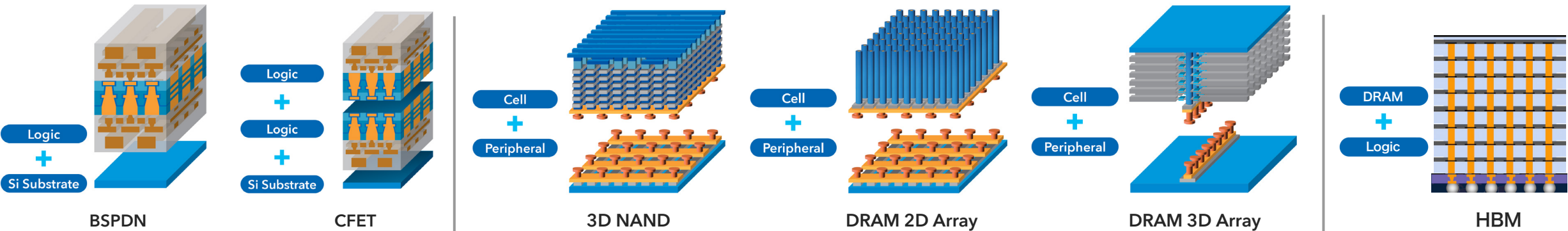
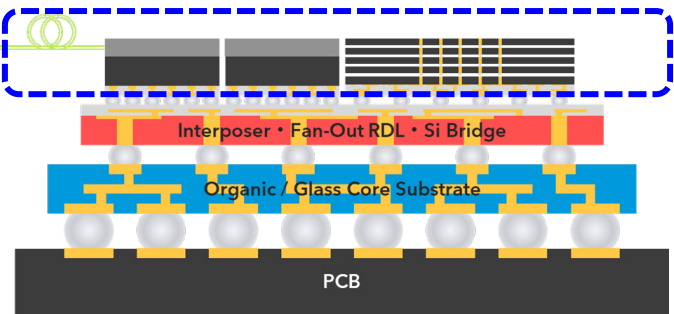
Initiatives in 3D packaging

Accelerating development of 3D packaging solutions

WoW bonding systems

Development started in FY2021 as part of the NEDO project

- Proprietary plasma (LIA) technology enabling low-temperature Cu-Cu bonding
- Integrated in-house cleaning unit (spin scrubber)
- Advanced wafer transfer control technology



Peripheral process equipment

Ongoing development of systems for processes and inspections related to WoW and CoW bonding

As WoW bonding is adopted in logic and memory devices, its applications are expected to grow significantly, driving greater demand for associated process and inspection solutions.

Acquisition of an R&D business in wafer bonding from Nikon

(effective on September 30, announced October 31, 2025)


SCREEN Holdings

News Release

October 31, 2025

Acquisition of an R&D business in wafer bonding from Nikon

SCREEN Holdings Co., Ltd. (SCREEN HD, President & CEO: Masato Goto) hereby announces the acquisition of an R&D business in wafer bonding from Nikon Corporation (Nikon; headquarters: Tokyo; Representative Director and Chairman: Toshikazu Umatate), effective on September 30.

In the semiconductor advanced packaging field, expectations are rising for more high-precision wafer bonding to support the increasing demand for footprint- and energy-saving devices. Positioning advanced packaging as a focus field, in addition to the sales of direct imaging systems and coater/dryer systems, we are working on the development and roll-out of low-temperature wafer bonding. The latest acquisition will allow us to combine Nikon's ultra-high-precision bonding technology with our proprietary technology as we seek to lead the world in bonding technology and establish a presence in this field.

Under the current medium-term management plan, Value Up Further 2026, covering the three fiscal years ending March 2027, SCREEN has been investing intensively for growth. In particular, we focus on advanced packaging as a new business field with a high growth potential, leading to the latest acquisition. The acquisition has already been reflected in the business plan for this fiscal year and therefore will not impart our earnings forecasts.

SCREEN will continue serving diverse client needs in the semiconductor packaging industry and contribute to its further development.

Overview of the acquisition

1. Acquired business

Nikon's R&D business in wafer bonding

2. Acquired from

NIKON CORPORATION
Headquarters: 1-5-20 Nishioi, Shinagawa-ku, Tokyo, Japan
Representative Director and Chairman: Toshikazu Umatate
Capitalization: JPY 65,476 million (as of March 31, 2025)
Established: July 25, 1917

3. Date of agreement

August 14, 2025

4. Date of acquisition

September 30, 2025



NIKON CORPORATION

Information

Transfer of research and development business for semiconductor wafer bonding technology

October 31, 2025

TOKYO - Nikon Corporation (Nikon) announced that it has entered into a transfer agreement with SCREEN Holdings Co., Ltd. (SCREEN) regarding Nikon's research and development business for semiconductor wafer bonding technology as follows.

Background of the transfer

Wafer bonding is a technology that is attracting attention as a way to improve semiconductor performance. SCREEN and Nikon have been discussing future collaborations regarding this technology. As a result, Nikon has concluded that transferring the technology to SCREEN is the best option, leading to the signing of this agreement. Nikon and SCREEN will continue to strengthen our collaboration, aiming to further refine the technology and quickly implement it in actual semiconductor manufacturing.

Transfer details

Nikon's semiconductor wafer bonding technology, know-how, intellectual property, etc.

Overview of the transferee

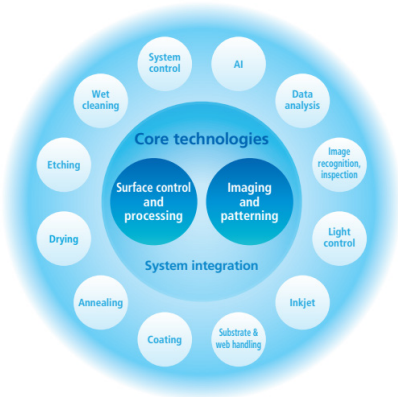
Company name	SCREEN Holdings Co., Ltd.
Head office location	Tenjinkita-machi 1-1, Teranouchi-agaru 4-chome, Horikawa-dori, Kamigyo-ku, Kyoto, Japan
Representative	Masato Goto, President and Chief Executive Officer (CEO)
Capitalization	54.0 billion yen (As of March 31, 2025)
Date of establishment	October 11, 1943

Source: News releases of the respective companies.

Advantages of our wafer-on-wafer (WoW) bonding system



SCREEN



Nikon's ultra-high precision alignment units leveraging the FEOL exposure technology

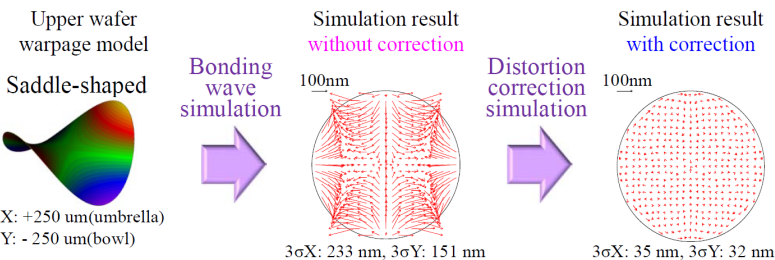
SCREEN's wet clean units (spin scrubbers)

Plasma technology (LIA) enabling low-temperature Cu-Cu bonding

* Enable the formation of an oxide-free, active Cu bonding surface with minimal damage

Distortion removal mechanism

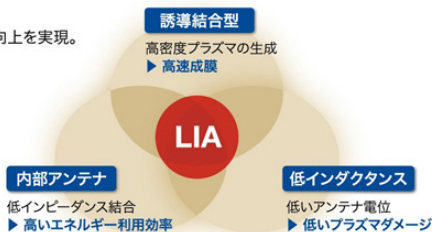
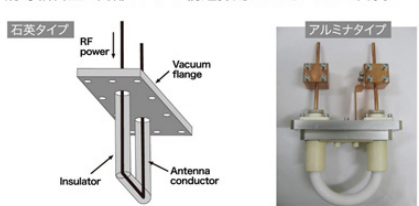
Wafer transport system



Source: H. Mitsuishi et al., "50 nm Overlay Accuracy for Wafer-to-wafer Bonding by High precision Alignment Technologies," 2023 IEEE 73rd Electronic Components and Technology Conference

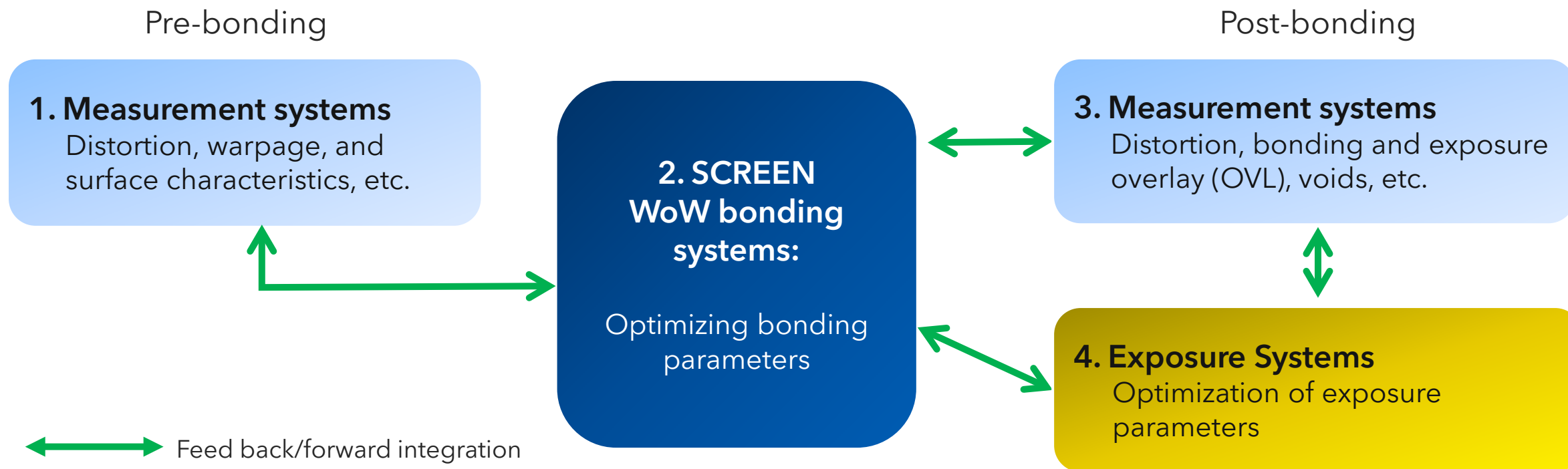
Low Inductance Antenna

誘導結合型と内部アンテナ構造採用により、プラズマ密度とエネルギー効率の向上を実現。



By combining both technologies, we are positioned to address the evolving market demands for WoW bonding systems, which are expected to become increasingly advanced and complex.

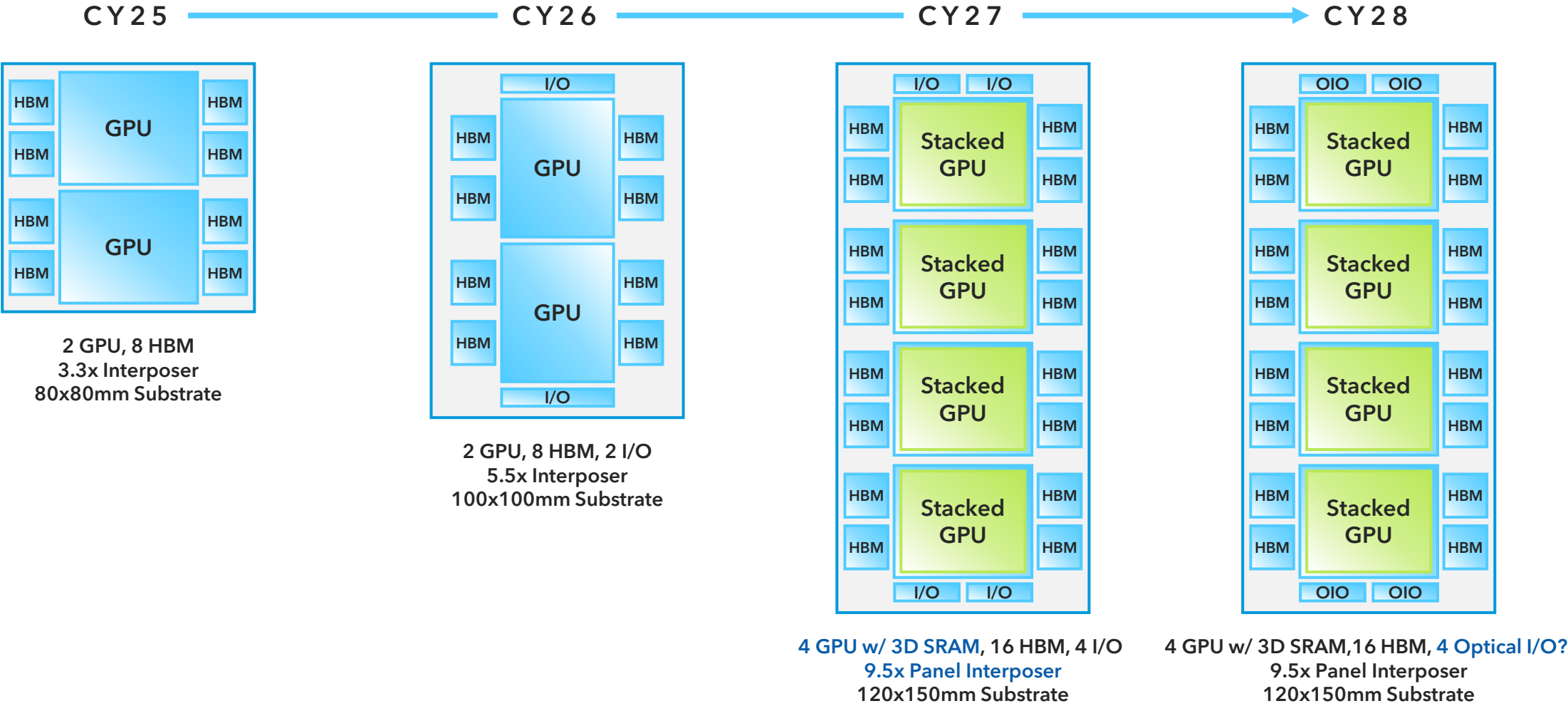
Feed back/forward integration across process steps



*With increasingly stringent bonding accuracy requirements, demand for single-wafer optimization is rising.
Driving innovation with a focus on integration with peripheral processes and metrology systems.*

Initiatives in 2.xD packaging

Ongoing shift toward larger chip sizes



The ongoing increase in chip size will further elevate the importance of PLP

2.xD solutions

LeVina



LeVina: Direct imaging system for next-generation patterning

Exposure area

LeVina-h	≦ 620 x 650mm
LeVina-i	≦ 620 x 650mm

New

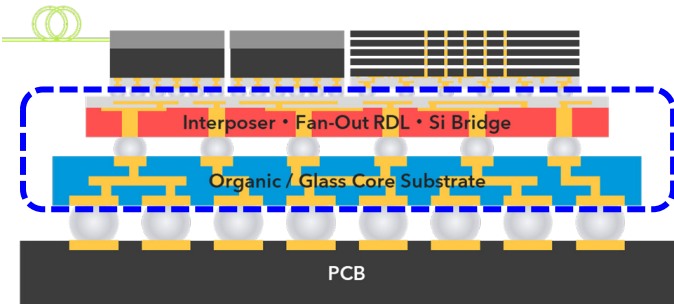
LEMOTIA



Lemotia: Slit coater system for panel-level packaging (PLP)

Panel size

LM-6000	600 x 600mm or 510 x 515mm
LM-3000	310 x 310mm or 300 x 300mm



Demonstration for PLP

A demonstration space for Panel Level Package will be constructed at SCREEN Hikone Site.
Panel Level Packaging (PLP) デモンストラーションスペースを
SCREEN 彦根事業所内に構築

Supported Processes
対応工程プロセス

Liquid Photoresist
液体光阻剤

Coating → Vacuum Dry → Pre Bake → Exposure → Development → Post Bake → Cure

A screenshot of a 3D architectural rendering of a modern, multi-story industrial building with a glass facade and greenery around it.

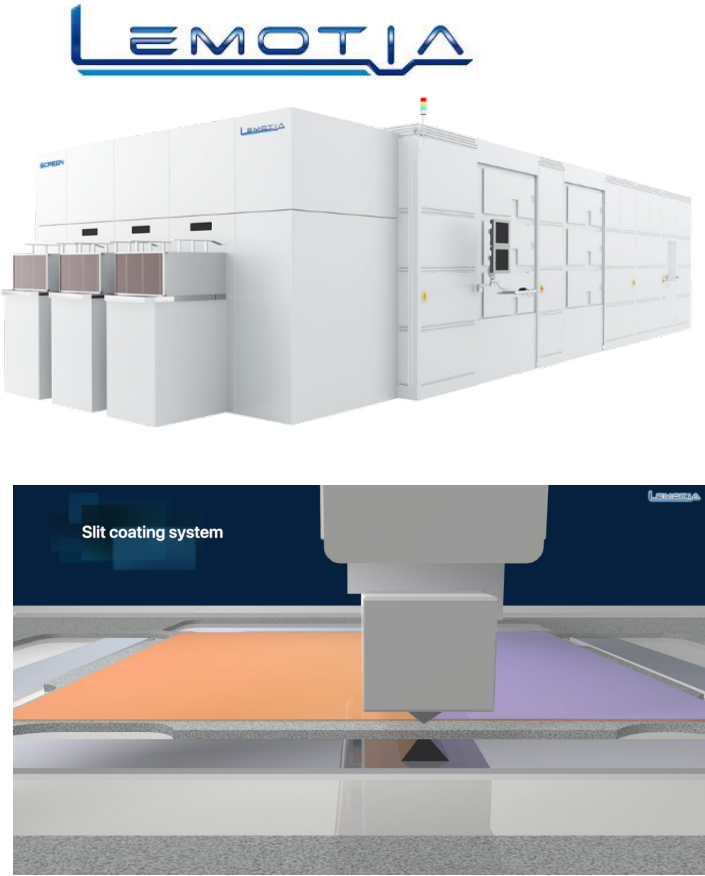
A demonstration space currently under construction in the Hikone Site—providing seamless solutions for the PLP processes

*Strengthening efforts in 2.xD solution development and marketing;
Lemotia has launched new offerings for 300 mm and 310 mm panels.*

Spin coater vs slit coater: Comparison

	Spin Coating 	Slit Coating 
Consistency	Difficult to coat corner edge	Compliant with the PLP standard 
Thick film coating	Difficult	Possible 
EBR	Required & difficult (Due to warpage)	Not required 
Low-pressure drying	Not required 	Required
Chemical usage	Large amount	Small amount 
Distortion adjustment	Required to develop	Already available 
Panel size expandability	Required to develop	Proven in the FPD market 

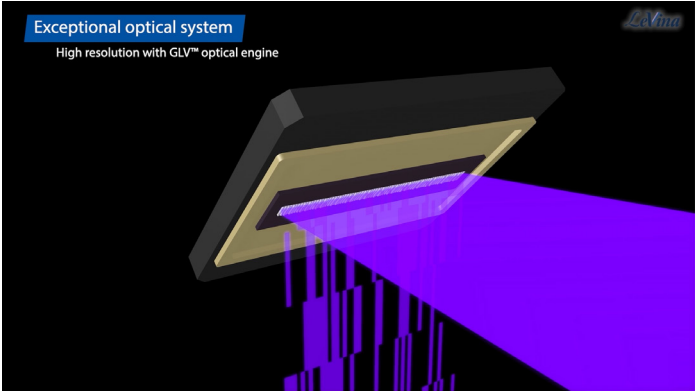
Note: Comparison based on SCREEN's in-house experiment.



Slit coater is better suited for panel coating due to consistency, less chemical use, and capability to adjusts panel distortion, accommodating the future expansion of panel size.

Our exposure systems

Application	PLP/WLP	PLP	PLP	FCBGA/FCCSP/MCM	FCBGA/MCP	FCCSP/MCM
Wavelength	375nmLD 	375nmLD 	405nmLD 	405nmLD 	Broad 	Broad 
Model	DW-3100 	LeVina-i 	LeVina-h 	LUPIOS 	Ledia Qs 	Ledia 8F 
Productivity						
Resolution (L/S)	 $\cong 1/1\mu\text{m}$	 $2/2\mu\text{m}$	 $5/5\mu\text{m}$	 $8/8\mu\text{m}$	 $10/10\mu\text{m}$	 $12/12\mu\text{m}$
Maximum Exposure Area	310 × 310 mm	620 × 650 mm	620 × 650 mm	546 × 635 mm	587 × 661 mm	610 × 661 mm
Overlay (Ave + 3 σ)	 0.5 μm	 2.0 μm	 3.5 μm	 3.5 μm	 5 μm	 5 μm



LeVina and the DW series feature SCREEN’s GLV™ optical engine

Expanding our product lineup further to address diversified exposure needs in advanced packaging.

Increasing SCREEN's presence and business scale in advanced packaging

2.xD

Focusing on expanding the product lineup of exposure and coater/dryer systems and their marketing

3D

Accelerating the development of WoW bonding systems as well as peripheral systems

Innovation for a Sustainable World

